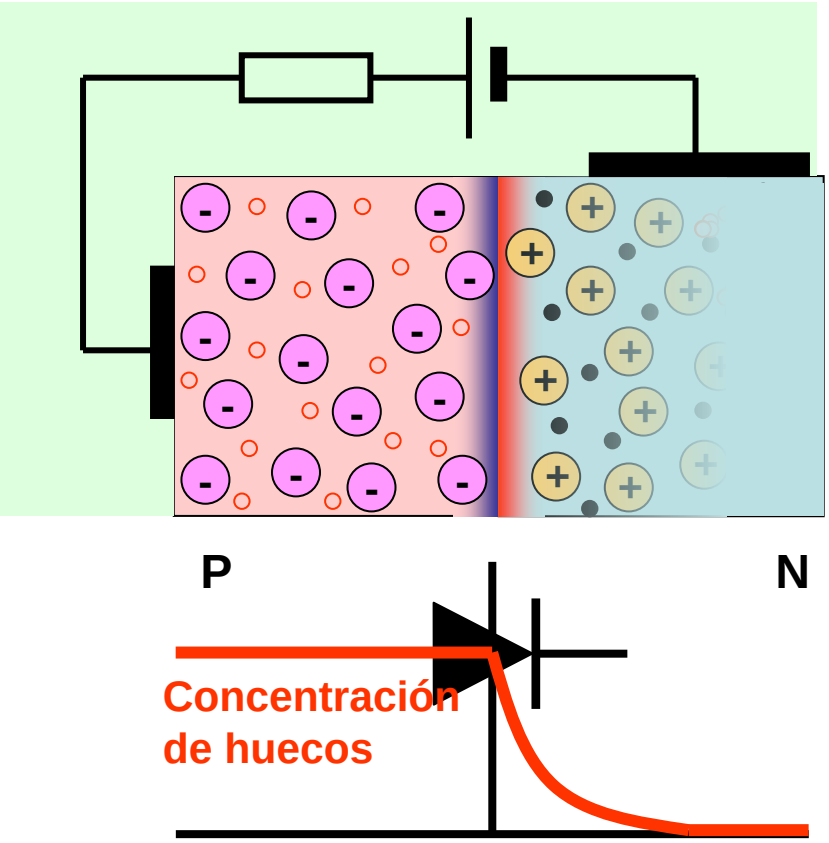
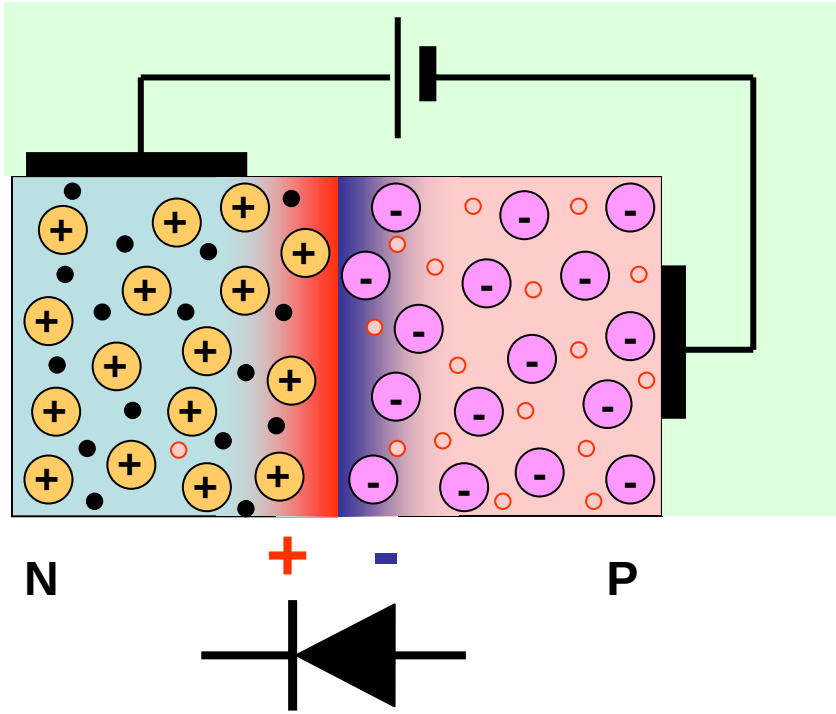
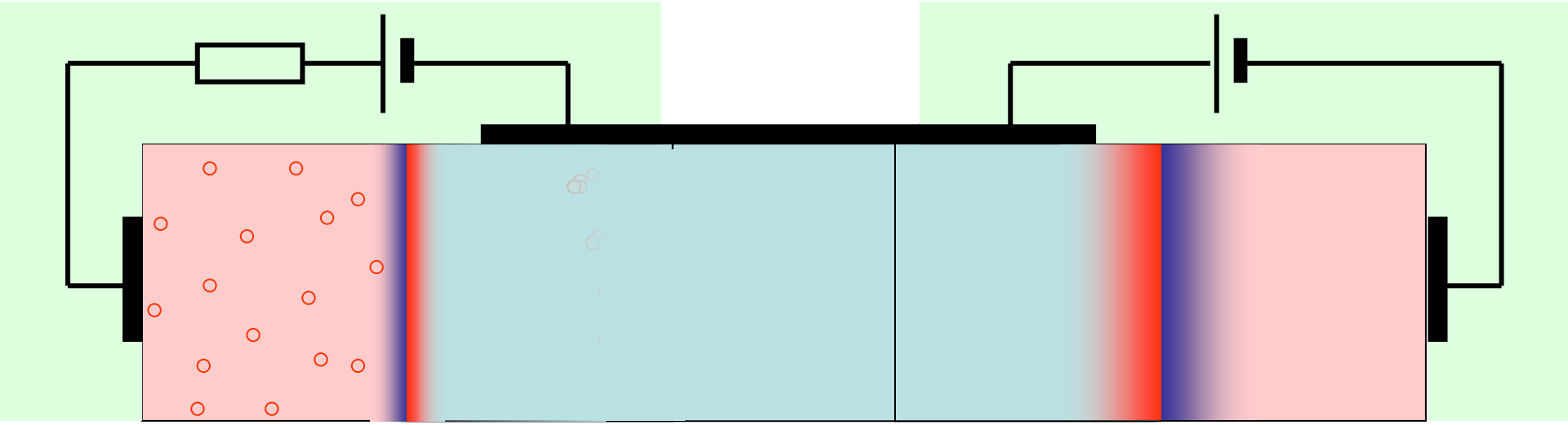
EL TRANSISTOR BIPOLAR BJT

Principio de funcionamiento del transistor bipolar





Principio de funcionamiento del transistor bipolar



Si la zona central es muy ancha, el comportamiento es similar a dos diodos en oposición. El funcionamiento de la primera unión no afecta a la segunda.

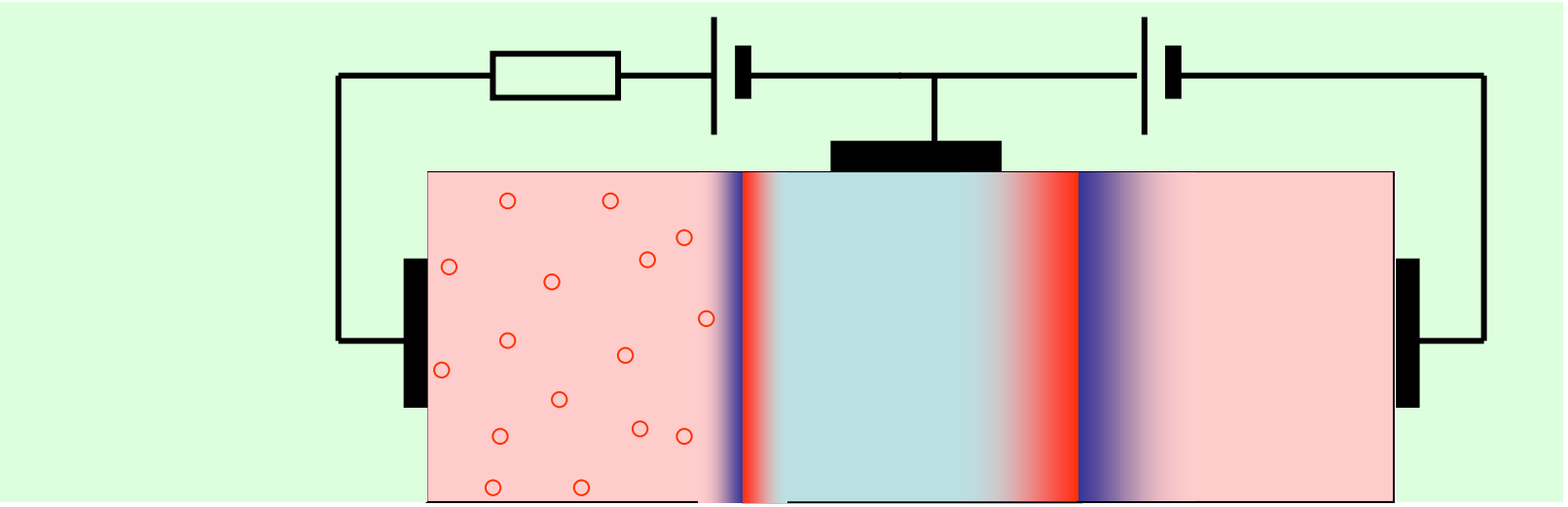
>

Principio de funcionamiento del transistor bipolar

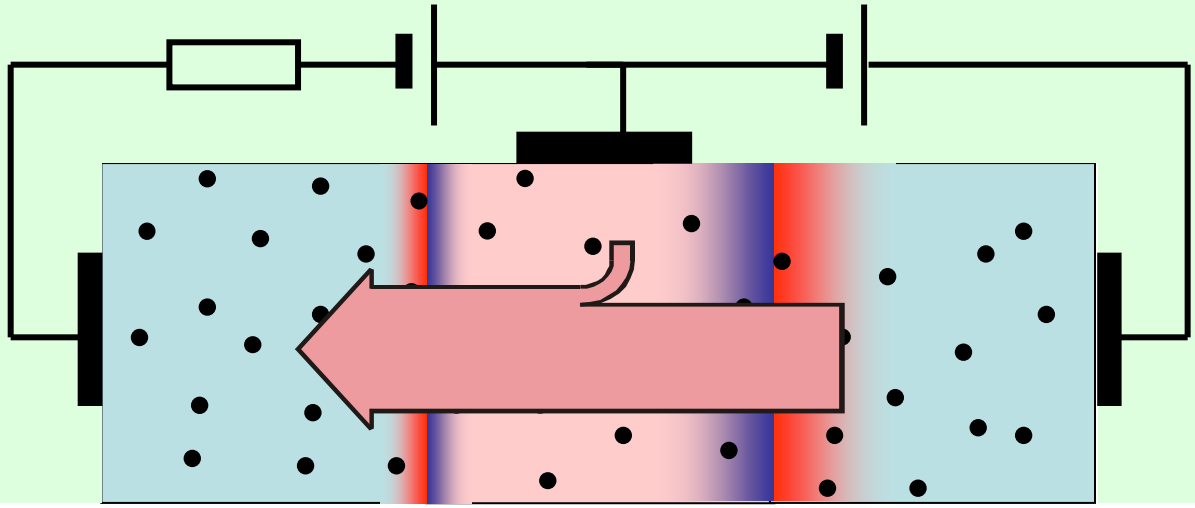
Unión o Juntura en común

>

Principio de funcionamiento del transistor bipolar

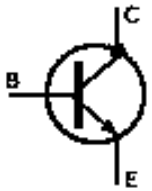


Principio de funcionamiento del transistor bipolar

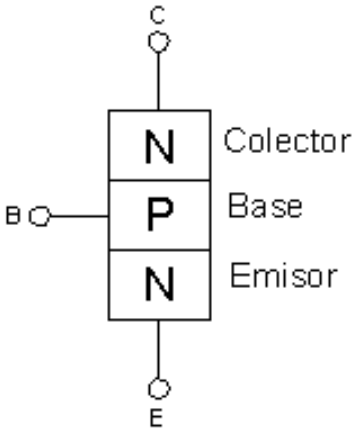


Transistor NPN

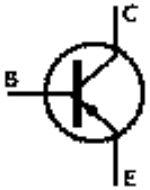
TRANSISTORES BPOLARES



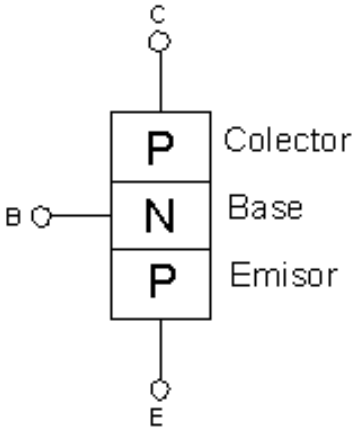
Transistor NPN



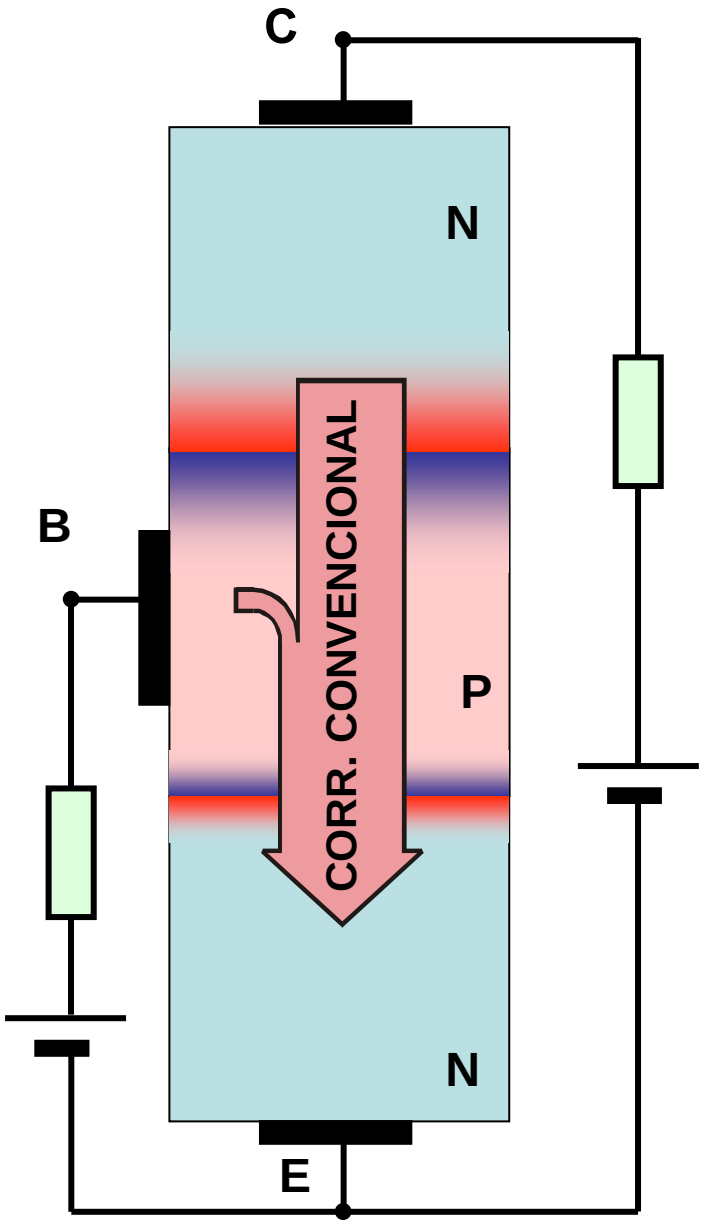
Estructura de un transistor NPN

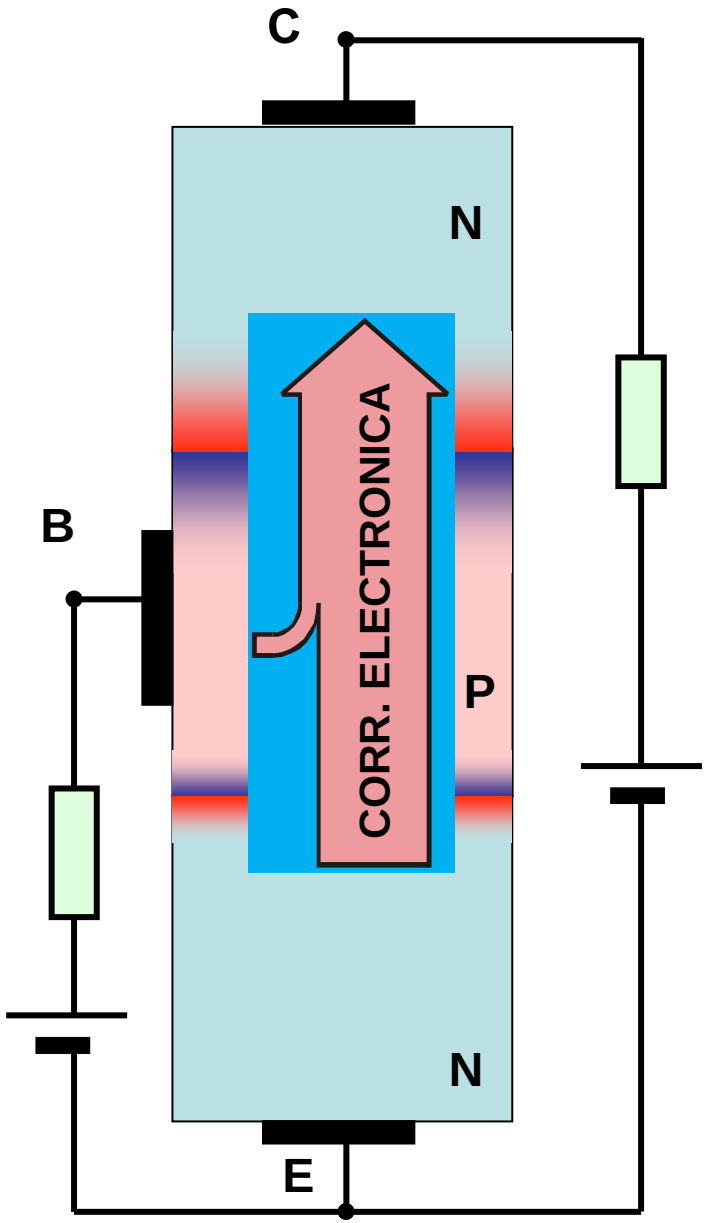


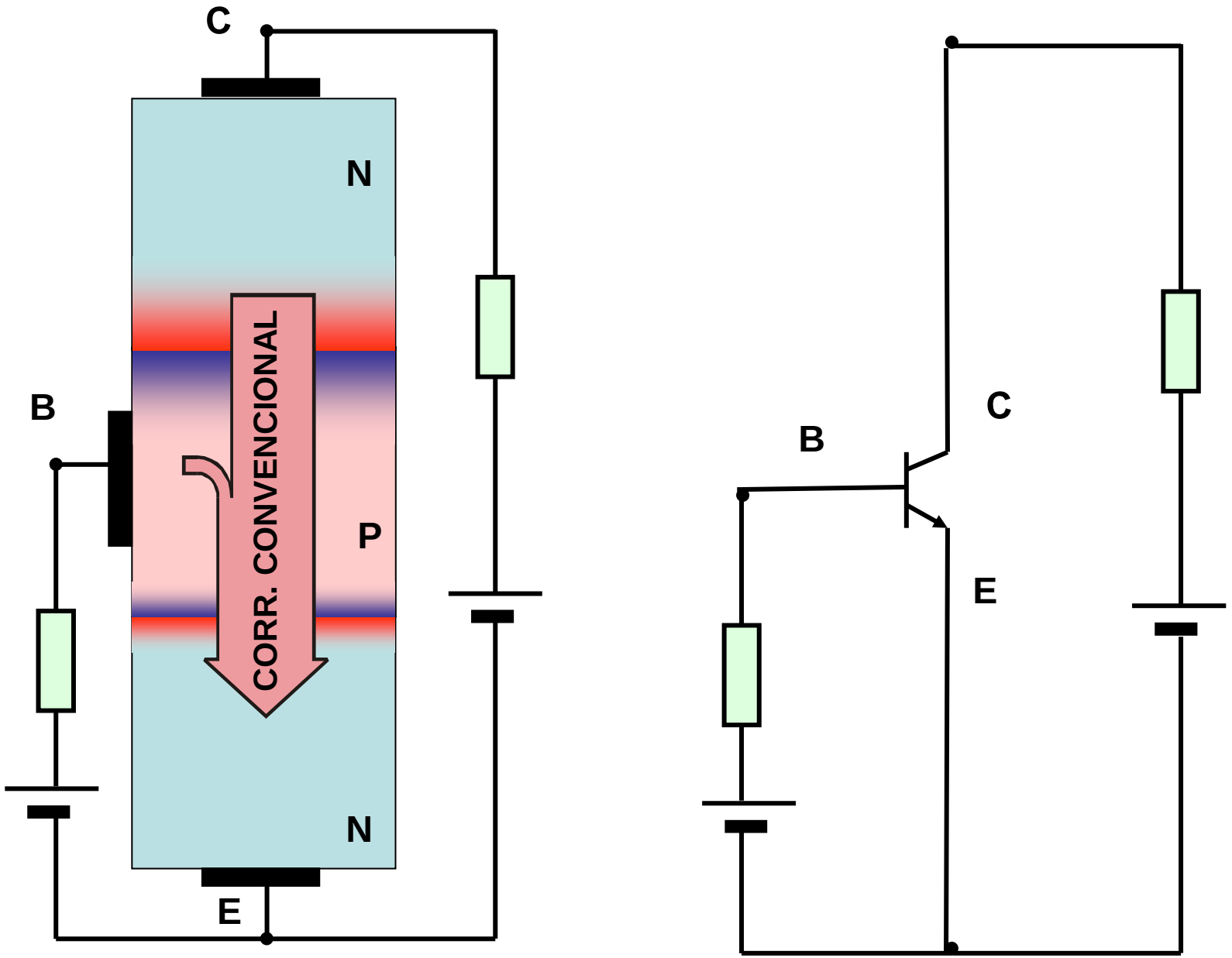
Transistor PNP



Estructura de un transistor PNP

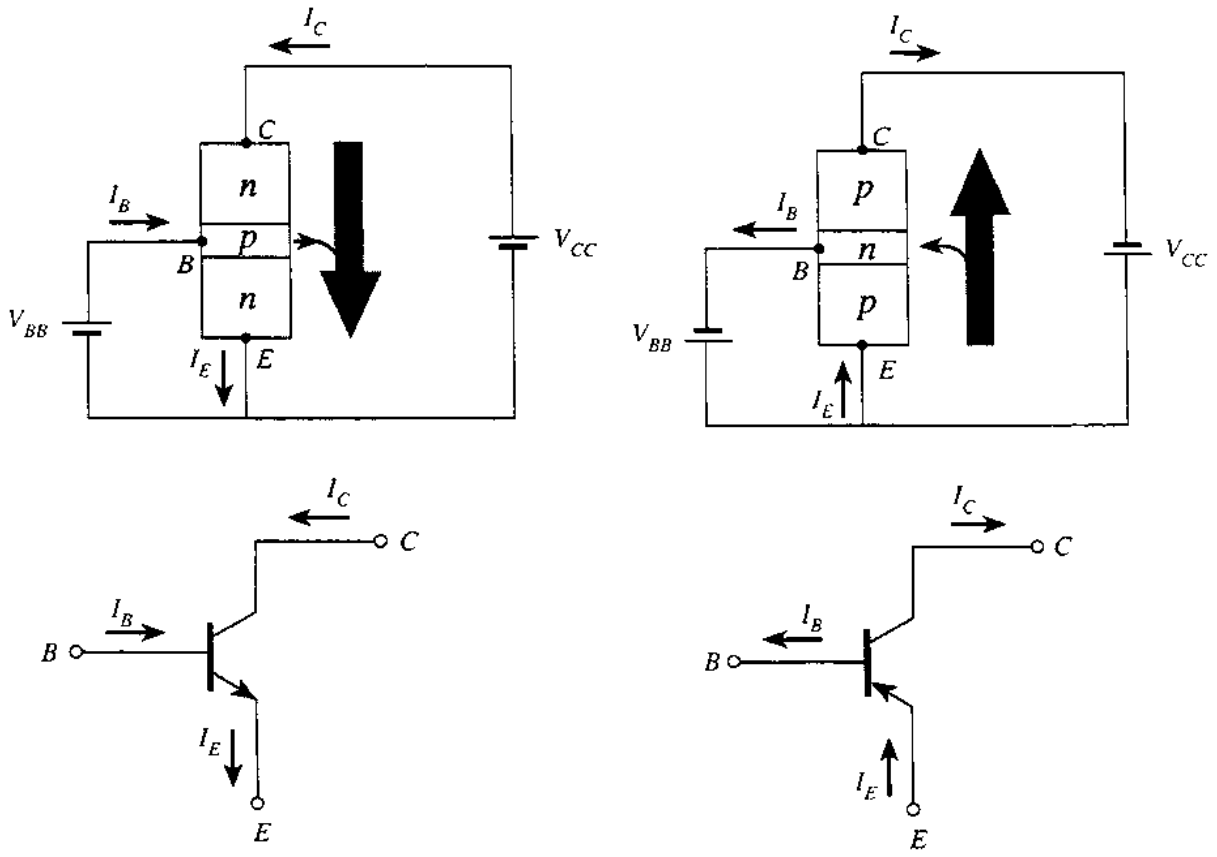

C
N
B
CORR. CONVENCIONAL
P
N
E


C
N
B
CORR. ELECTRONICA
P
N
E

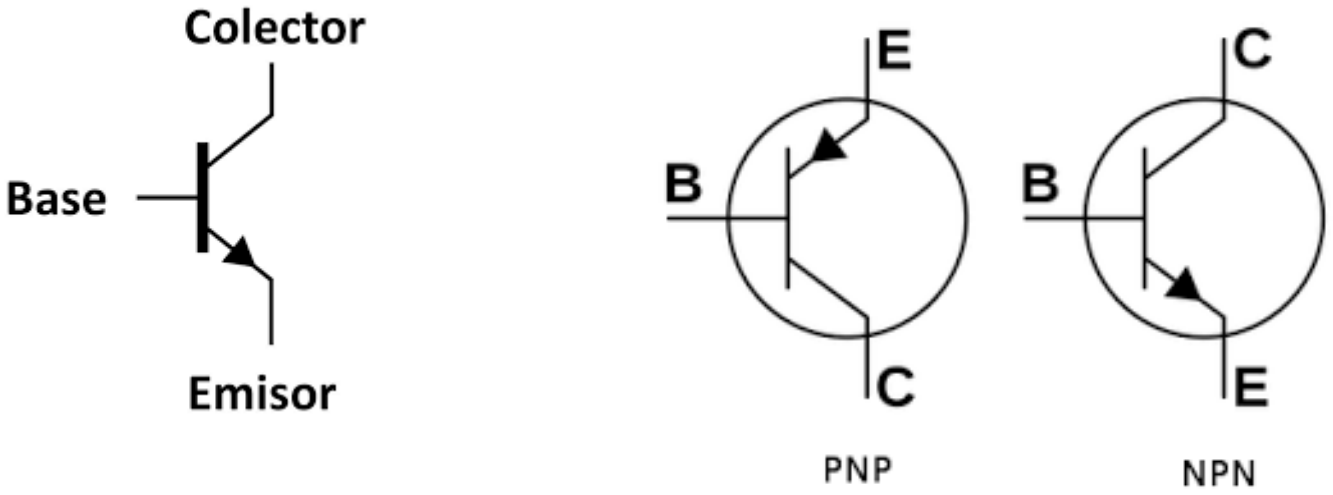

C
N
B
P
CORR. CONVENCIONAL
N
E
B
C
E

Configuración Emisor Común

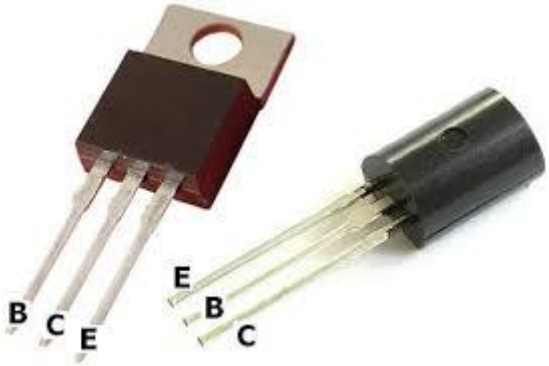
Configuración de emisor común para transistores *npn* y *pnp*.

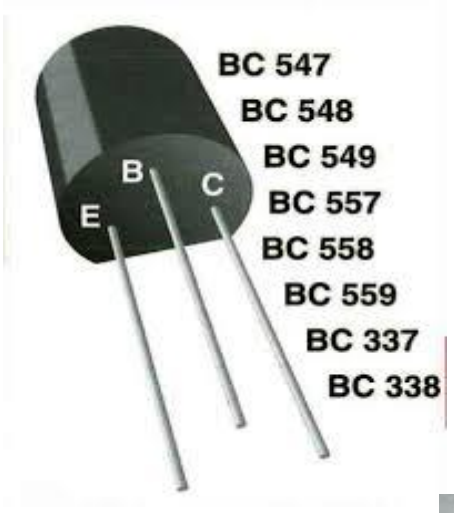


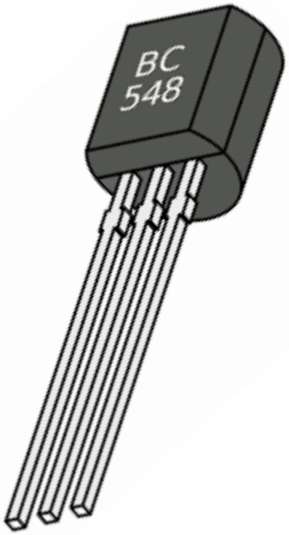
SIMBOLO DEL TRANSISTOR

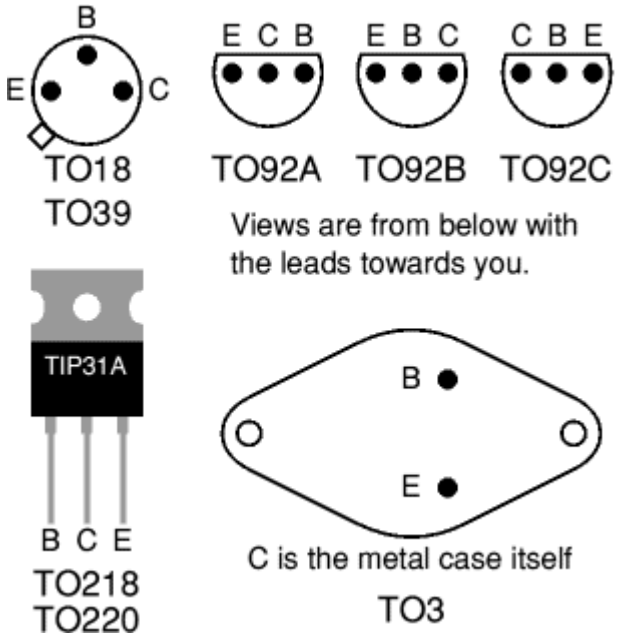


ENCAPSULADOS



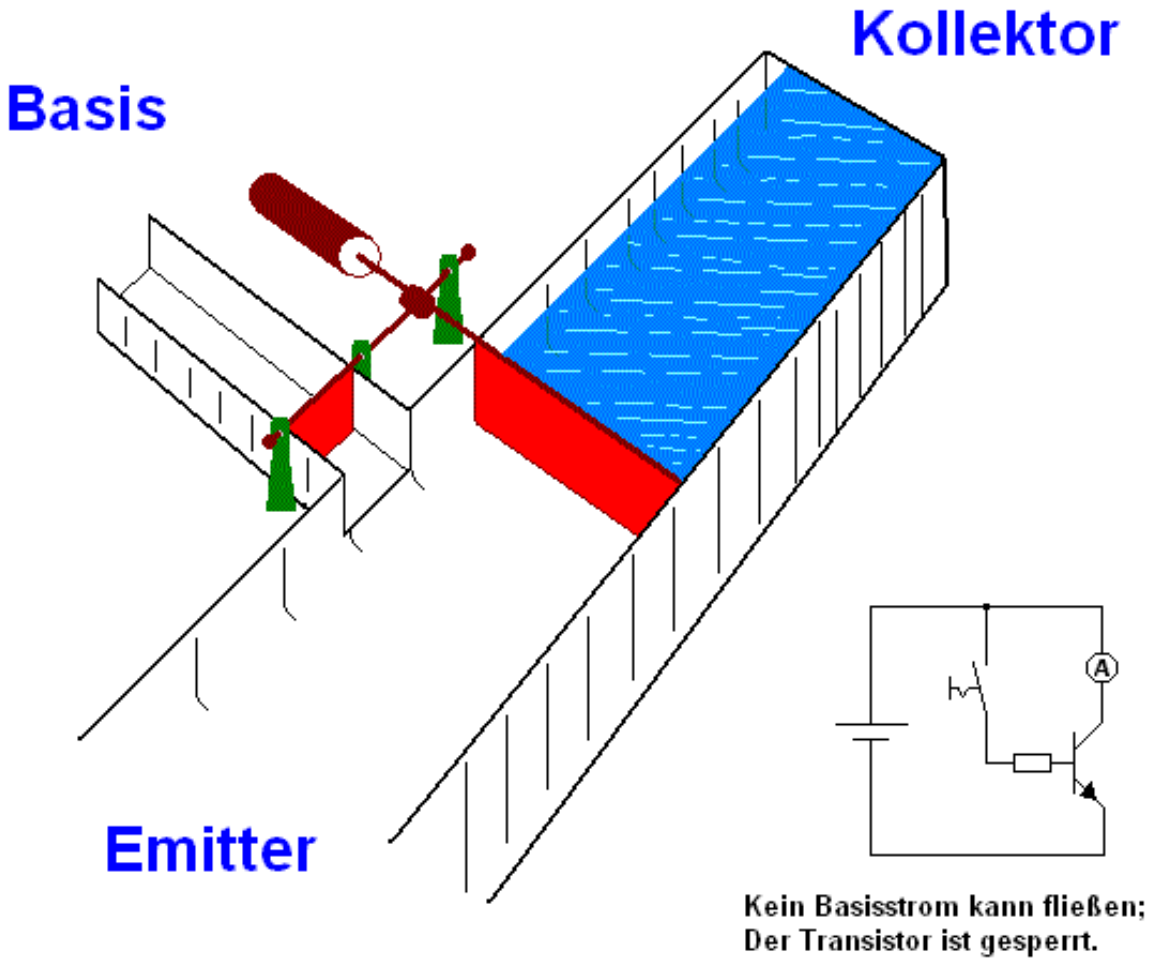






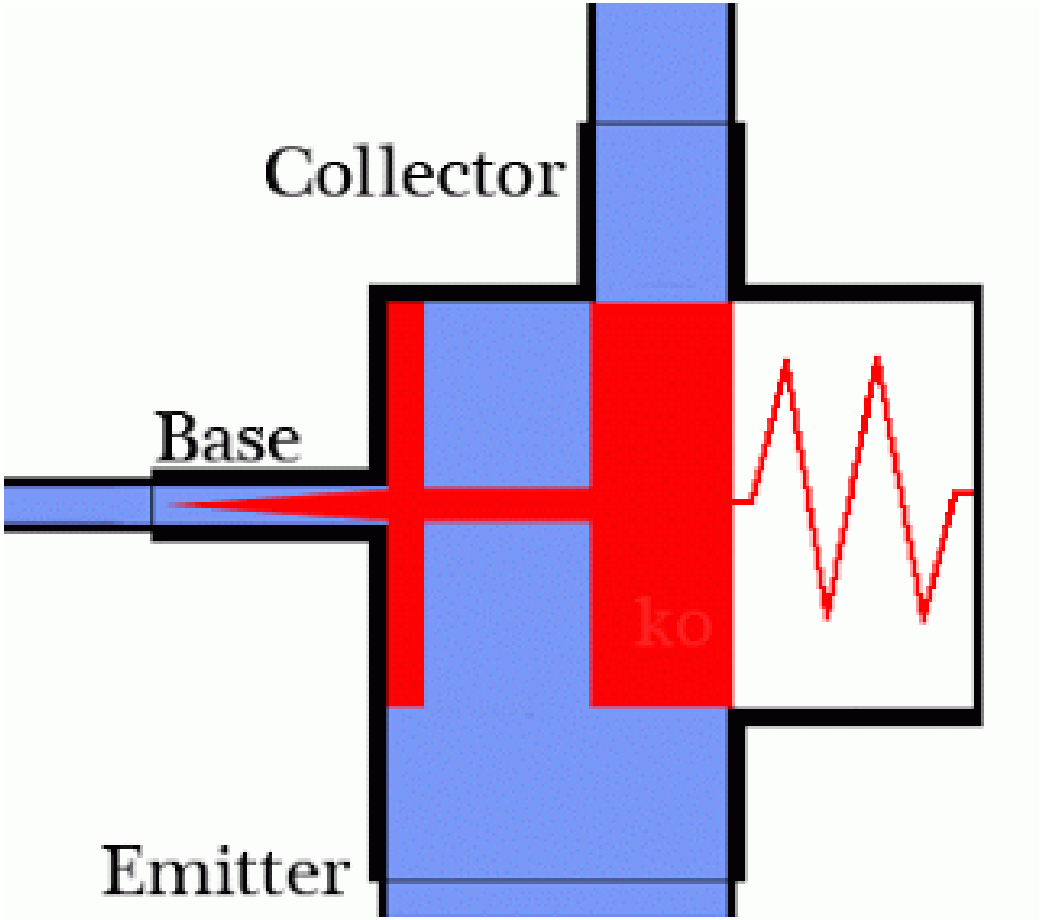
SIMULACION TRANSISTOR

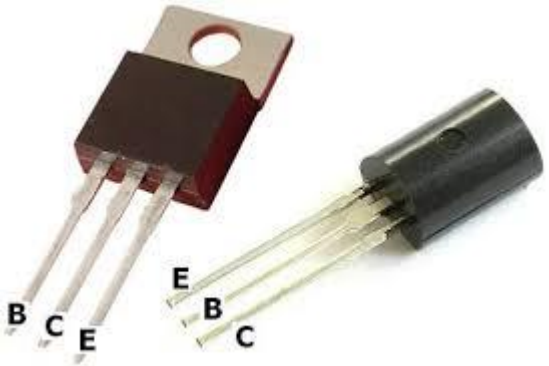
Analogía Hidráulica



SIMULACION TRANSISTOR

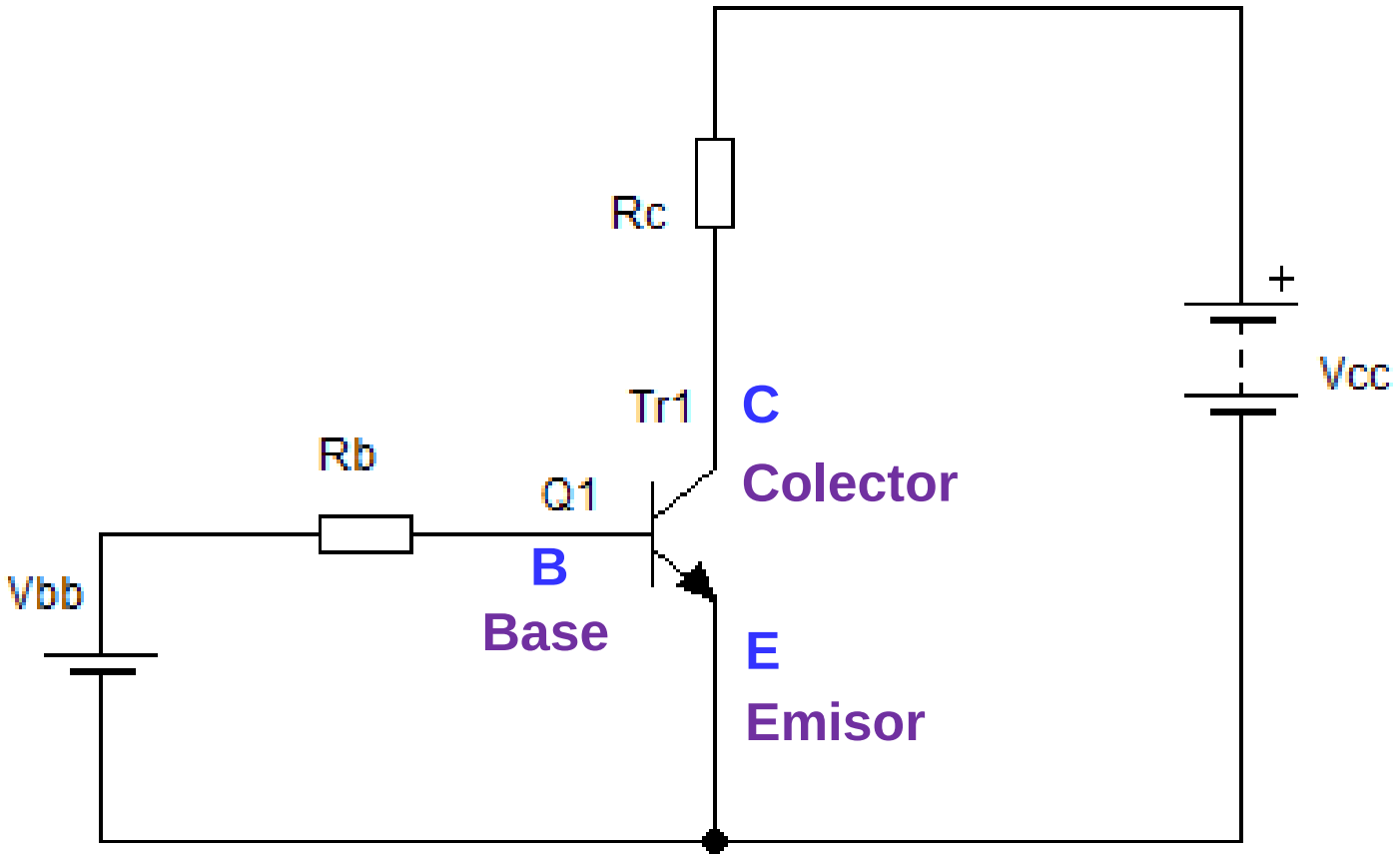
Analogía Hidráulica



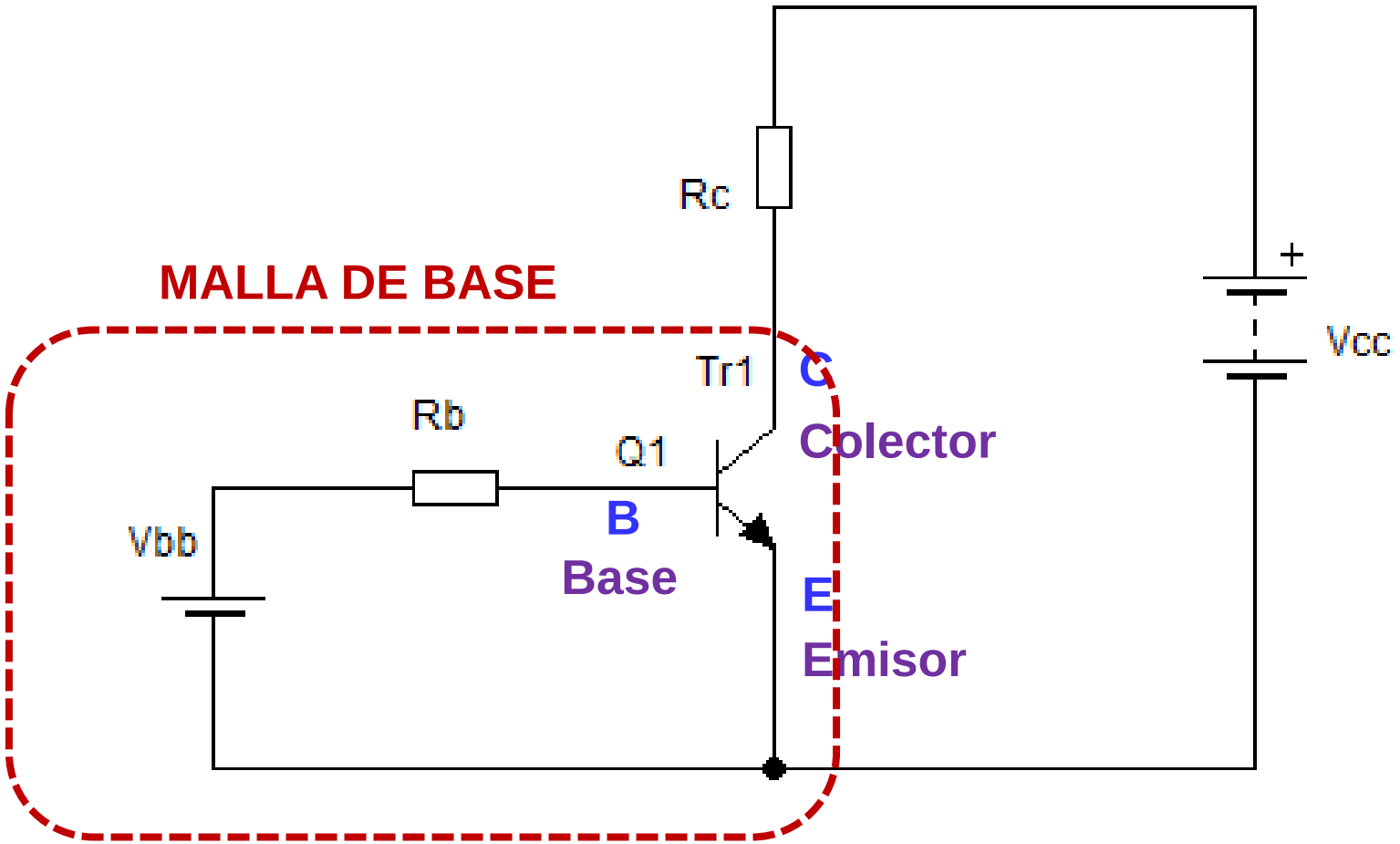


Corrientes en un Transistor

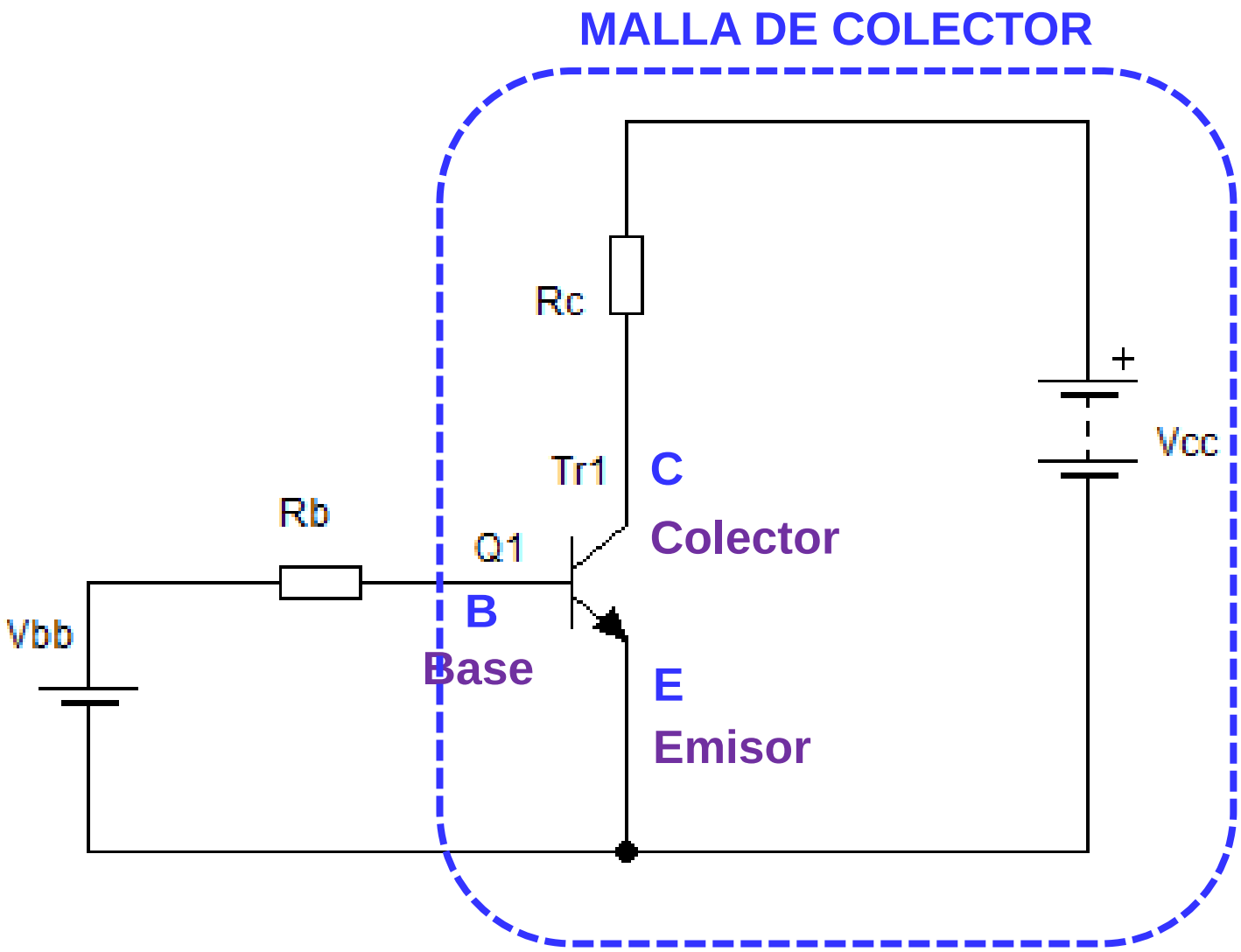
Configuración Emisor Común



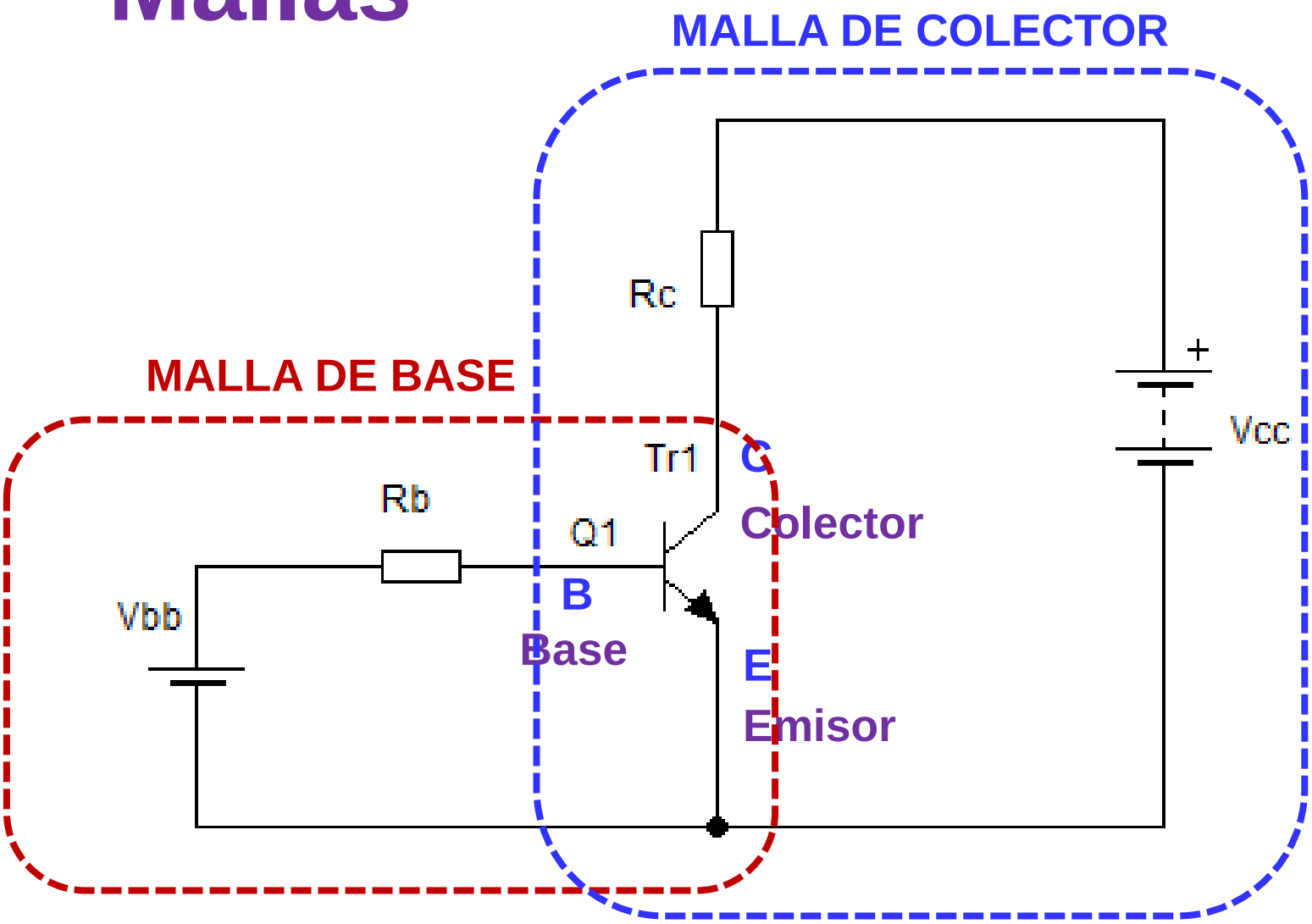
Malla de BASE



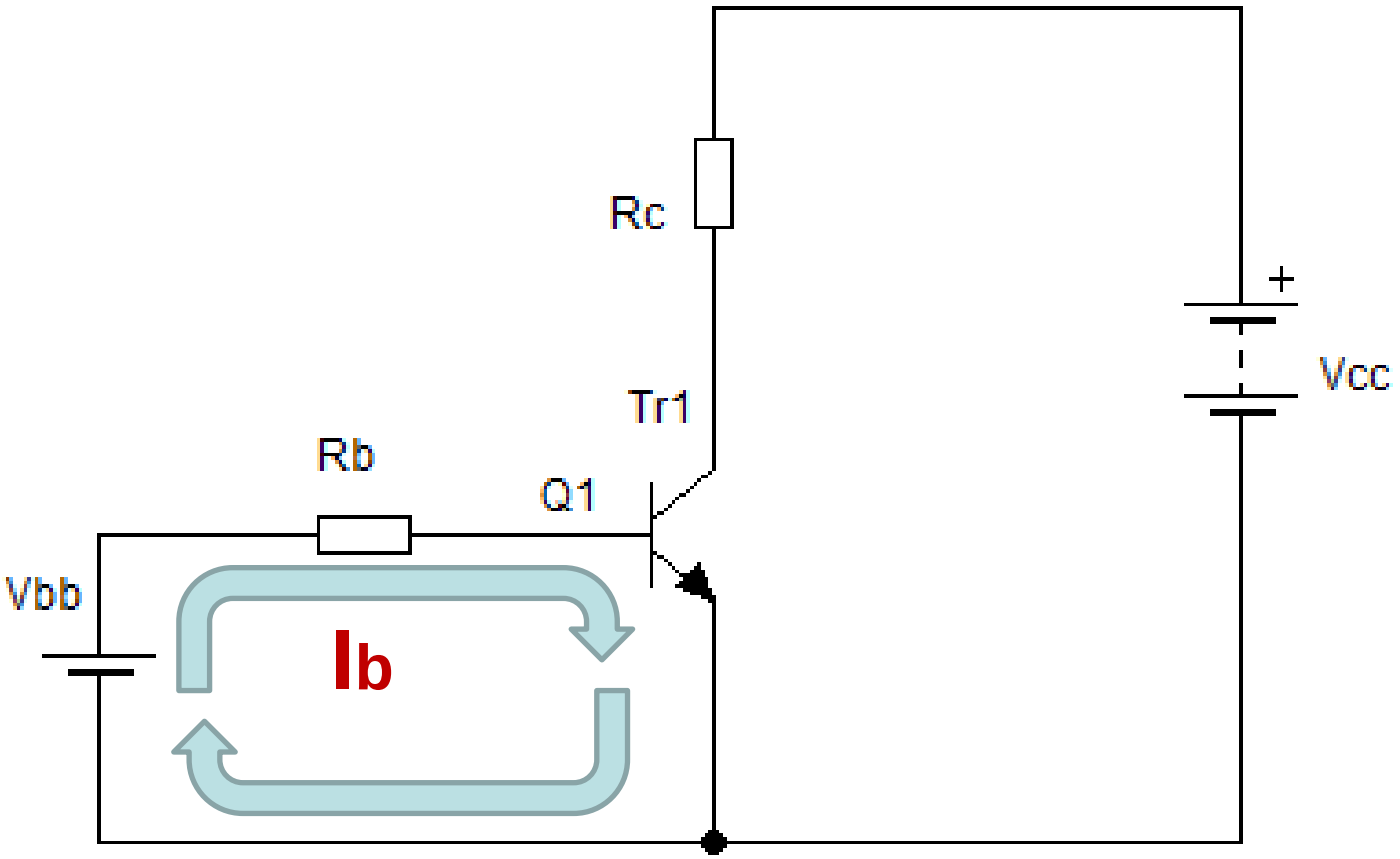
Malla de COLECTOR



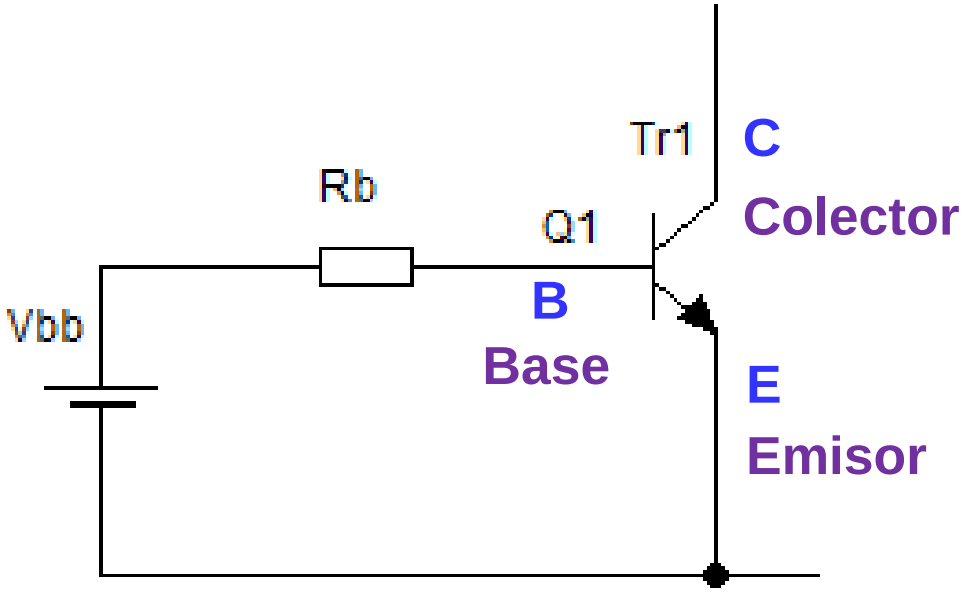
Mallas


MALLA DE COLECTOR
MALLA DE BASE
Rc
Rb
Vbb
Tr1
Q1
C
Colector
B
Base
E
Emisor
+
Vcc

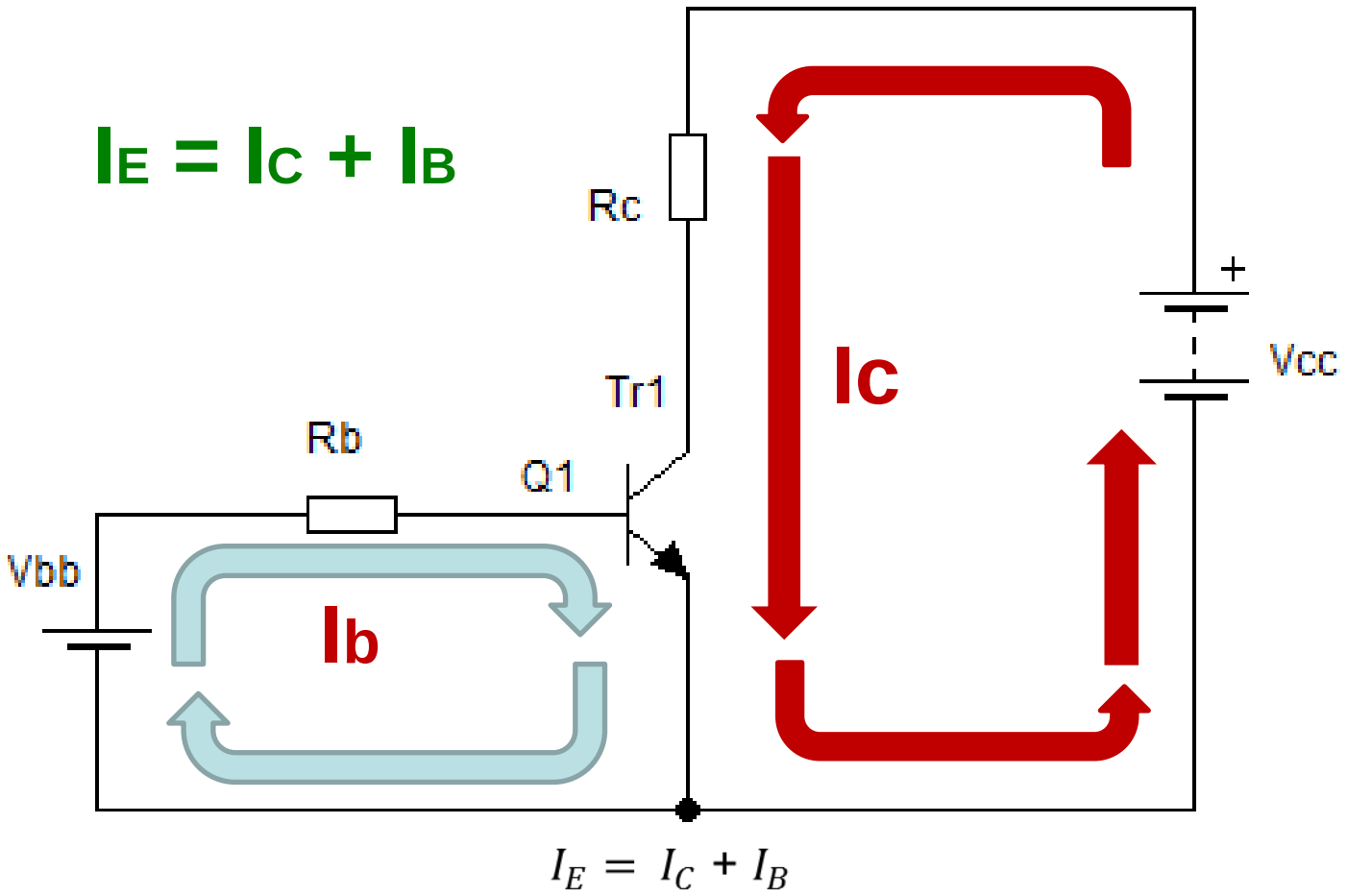
Corriente de Base



Malla de Base



Corrientes en un Transistor



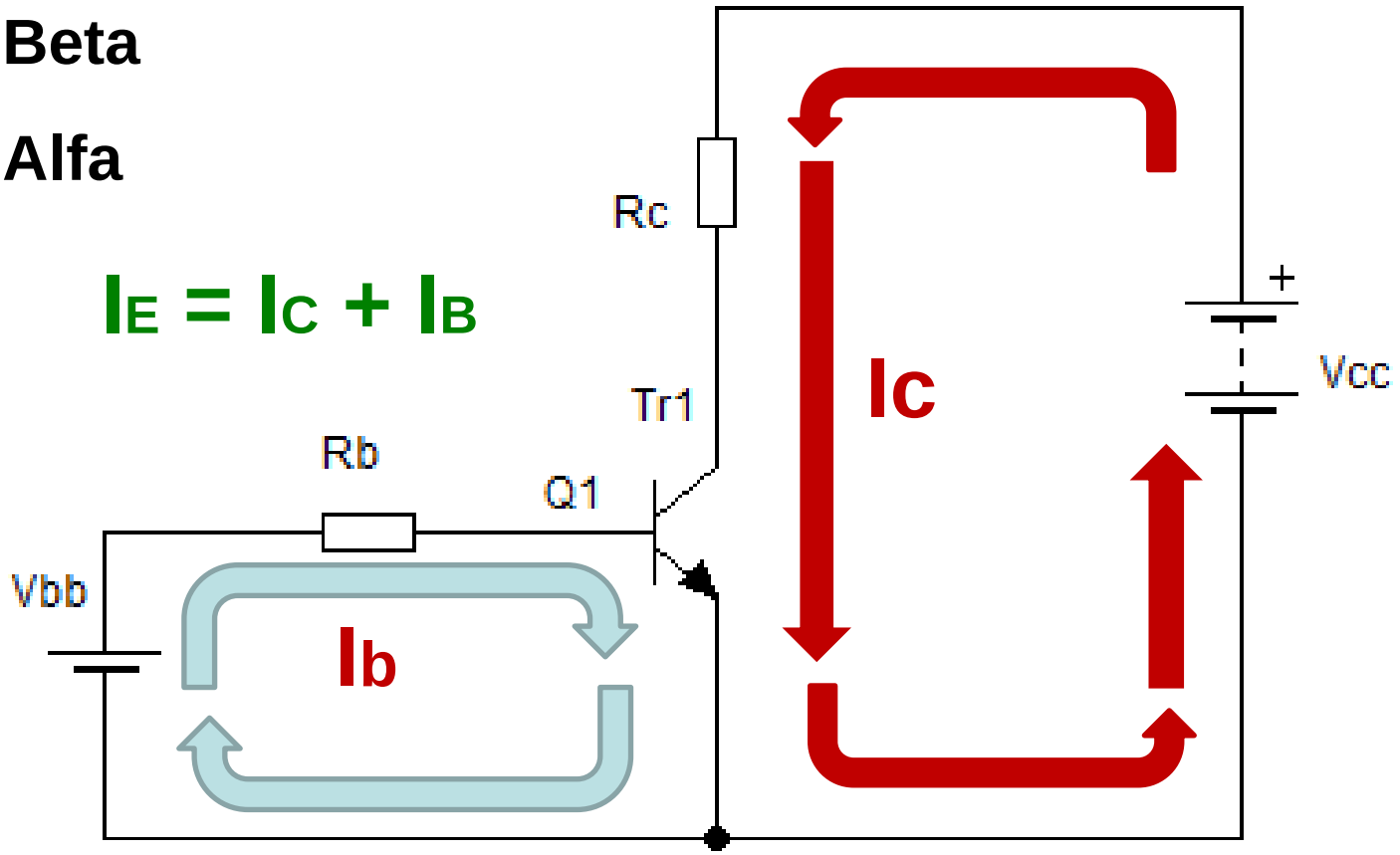
$$I_E = I_C + I_B$$

Corrientes en un Transistor

Beta

Alfa

$I_E = I_C + I_B$



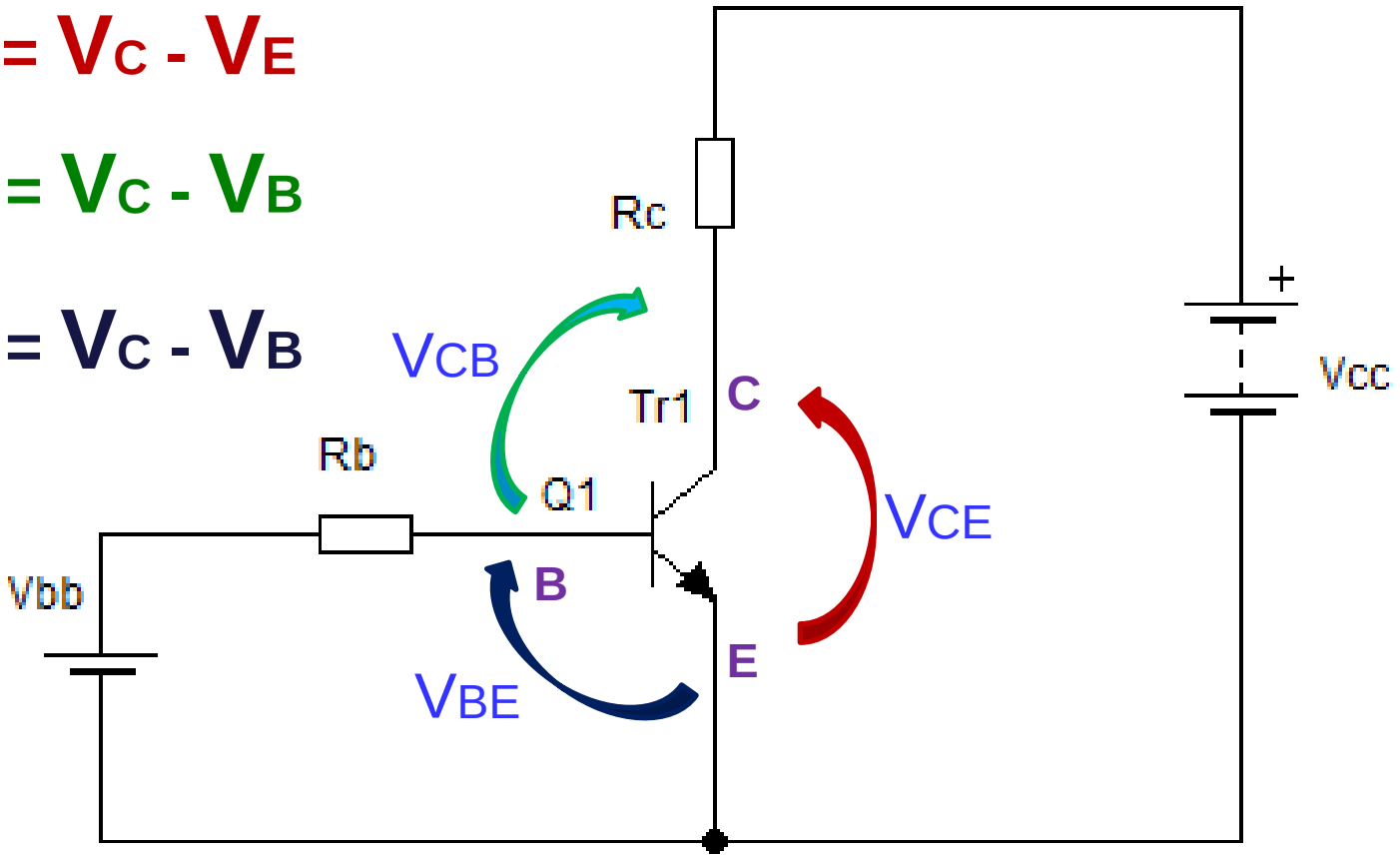
$$I_E = I_C + I_B$$

Tensiones en un Transistor

$V_{CE} = V_C - V_E$

$V_{CB} = V_C - V_B$

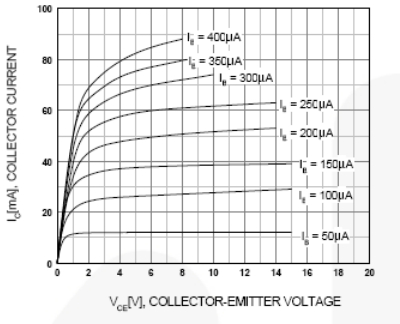
$V_{CB} = V_C - V_B$

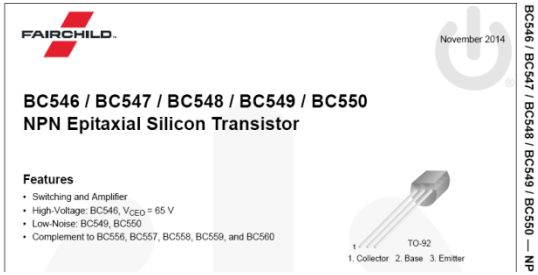


EL TRANSISTOR BIPOLAR BJT

HOJA DE DATOS TECNICOS

DATA SHEETS




FAIRCHILD

November 2014

BC546 / BC547 / BC548 / BC549 / BC550
NPN Epitaxial Silicon Transistor

Features
- Switching and Amplifier
- High-Voltage: BC546, V_{CEO} = 65 V
- Low-Noise: BC549, BC550
- Complement to BC556, BC557, BC558, BC559, and BC560

TO-92
1. Collector 2. Base 3. Emitter

BC546 / BC547 / BC548 / BC549 / BC550 — NP

DATOS TECNICOS

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter		Value	Unit
V_{CBO}	Collector-Base Voltage	BC546	80	V
		BC547 / BC550	50	
		BC548 / BC549	30	
V_{CEO}	Collector-Emitter Voltage	BC546	65	V
		BC547 / BC550	45	
		BC548 / BC549	30	
V_{EBO}	Emitter-Base Voltage	BC546 / BC547	6	V
		BC548 / BC549 / BC550	5	
I_C	Collector Current (DC)		100	mA
P_C	Collector Power Dissipation		500	mW
T_J	Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-65 to +150	°C

Electrical Characteristics

Values are at T_A = 25°C unless otherwise noted.

DATOS TECNICOS

Electrical Characteristics

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter		Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-Off Current		V_{CB} = 30 V, I_E = 0			15	nA
h_{FE}	DC Current Gain		V_{CE} = 5 V, I_C = 2 mA	110		800	
V_{CE}(sat)	Collector-Emitter Saturation Voltage		I_C = 10 mA, I_B = 0.5 mA		90	250	mV
			I_C = 100 mA, I_B = 5 mA		250	600	
V_{BE}(sat)	Base-Emitter Saturation Voltage		I_C = 10 mA, I_B = 0.5 mA		700		mV
			I_C = 100 mA, I_B = 5 mA		900		
V_{BE}(on)	Base-Emitter On Voltage		V_{CE} = 5 V, I_C = 2 mA	580	660	700	mV
			V_{CE} = 5 V, I_C = 10 mA			720	
f_T	Current Gain Bandwidth Product		V_{CE} = 5 V, I_C = 10 mA, f = 100 MHz		300		MHz
C_{ob}	Output Capacitance		V_{CB} = 10 V, I_E = 0, f = 1 MHz		3.5	6.0	pF
C_{ib}	Input Capacitance		V_{EB} = 0.5 V, I_C = 0, f = 1 MHz		9		pF
NF	Noise Figure	BC546 / BC547 / BC548	V_{CE} = 5 V, I_C = 200 µA, f = 1 kHz, R_G = 2 kΩ		2.0	10.0	dB
		BC549 / BC550			1.2	4.0	
		BC549	V_{CE} = 5 V, I_C = 200 µA, R_G = 2 kΩ, f = 30 to 15000 MHz		1.4	4.0	
		BC550			1.4	3.0	

axial Silicon Transistor

DATOS TECNICOS

h_{FE} Classification

Classification	A	B	C
h_{FE}	110 ~ 220	200 ~ 450	420 ~ 800

Typical Performance Characteristics

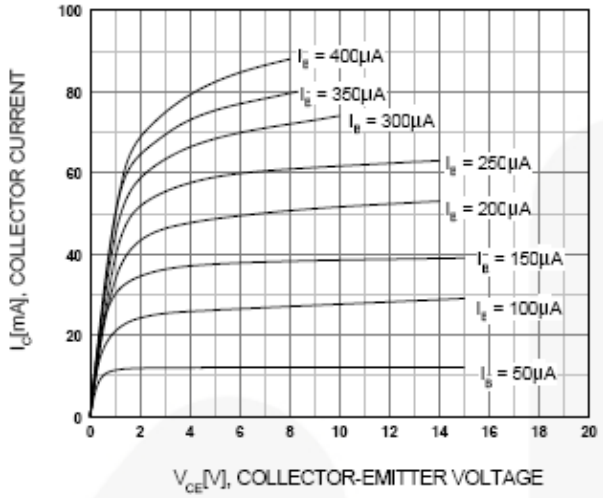


Figure 1. Static Characteristic

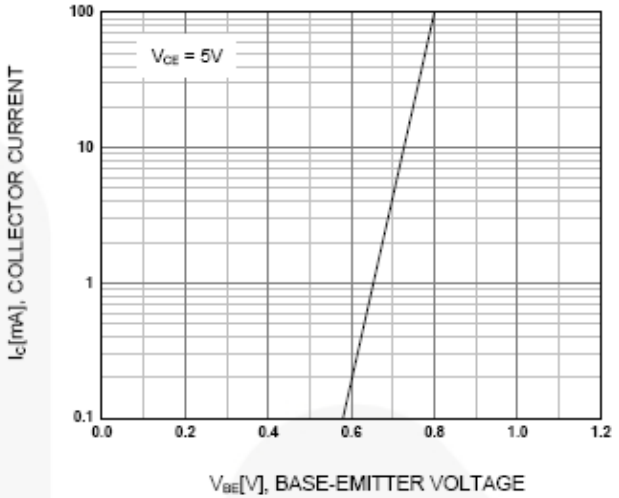


Figure 2. Transfer Characteristic

TRANSISTOR

CURVAS CARACTERISTICAS

TRANSISTOR

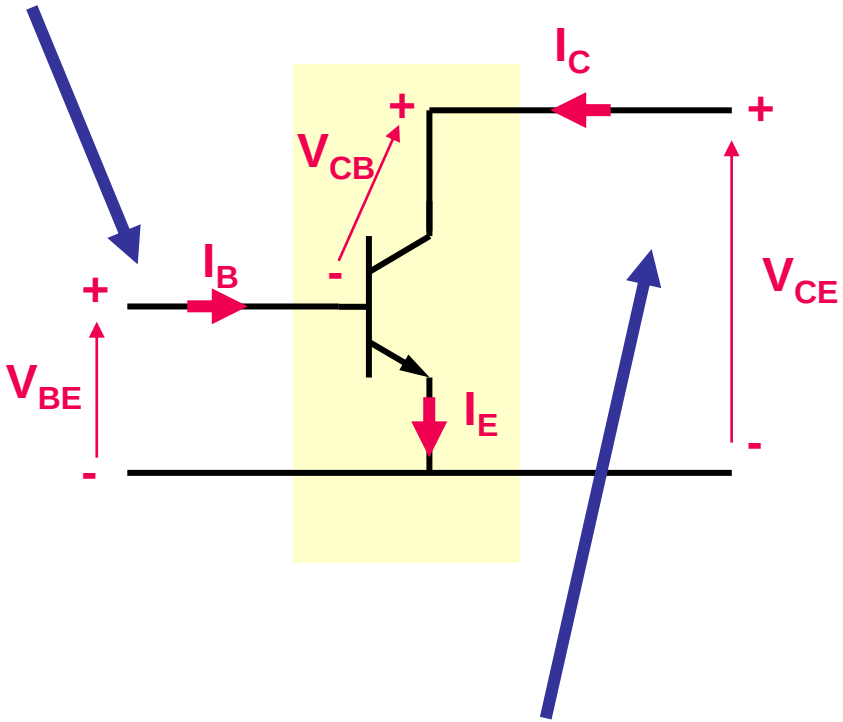
CURVA CARACTERISTICA

DE ENTRADA

Características eléctricas del transistor bipolar

Transistor NPN

$I_B = f(V_{BE}, V_{CE})$ **Característica de entrada**



$I_C = f(V_{CE}, I_B)$ **Característica de salida**

En principio necesitamos conocer 3 tensiones y 3 corrientes:

I_C, I_B, I_E

V_{CE}, V_{BE}, V_{CB}

En la práctica basta con conocer solo 2 corrientes y 2 tensiones.

Normalmente se trabaja con I_C, I_B, V_{CE} y V_{BE}.

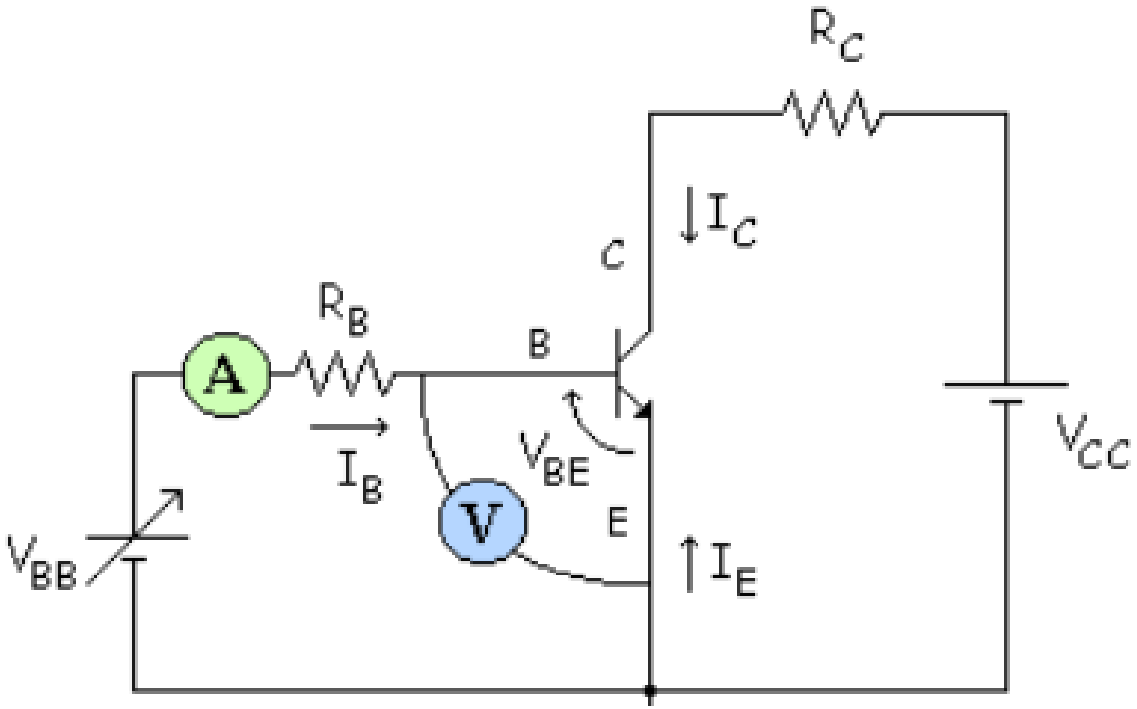
Por supuesto las otras dos pueden obtenerse fácilmente:

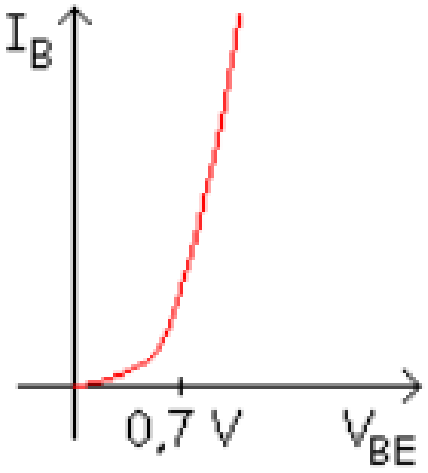
$$I_E = I_C + I_B$$

$$V_{CB} = V_{CE} - V_{BE}$$

Características del transistor bipolar

Determinación de la Curva Características de **Entrada**

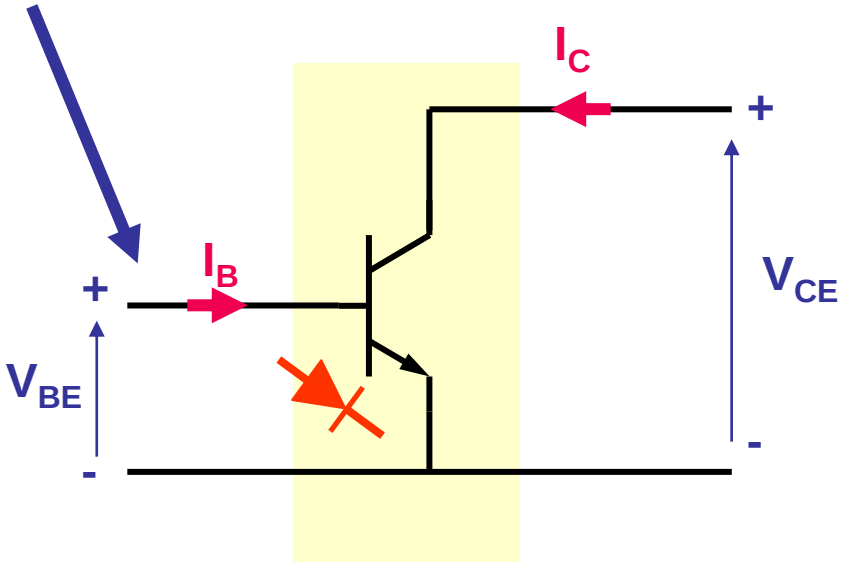


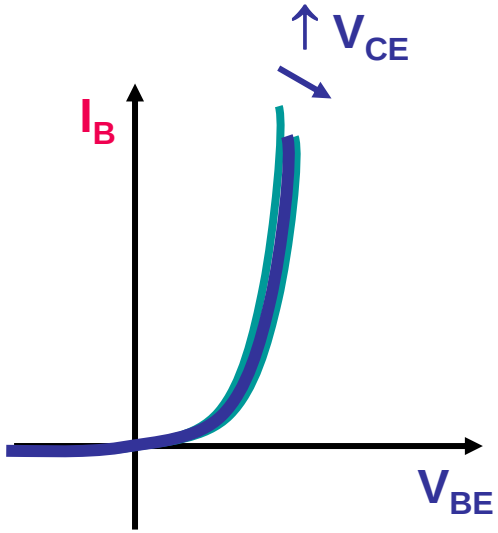


Curvas Características de Entrada

Transistor NPN

$I_B = f(V_{BE}, V_{CE})$ Característica de entrada



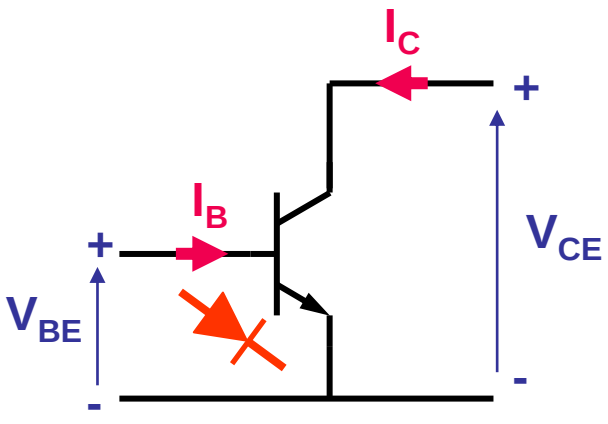


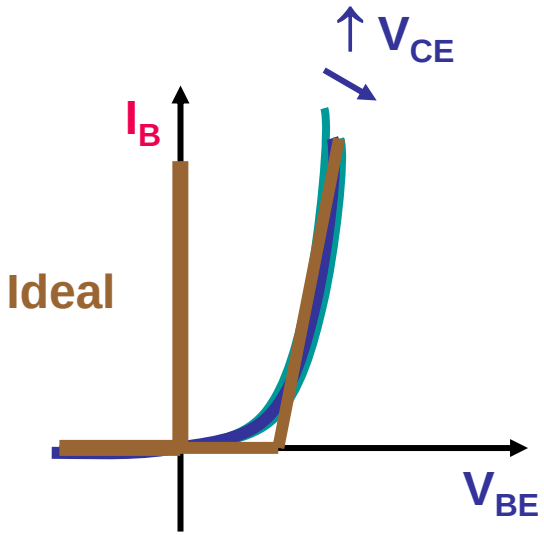
Entre base y emisor el transistor se comporta como un diodo.

La característica de este diodo depende de V_{CE} pero la variación es pequeña.

Curvas Características del transistor bipolar

Transistor NPN: linealización de la característica de entrada





La característica de entrada corresponde a la de un diodo y se emplean las aproximaciones lineales vistas anteriormente.

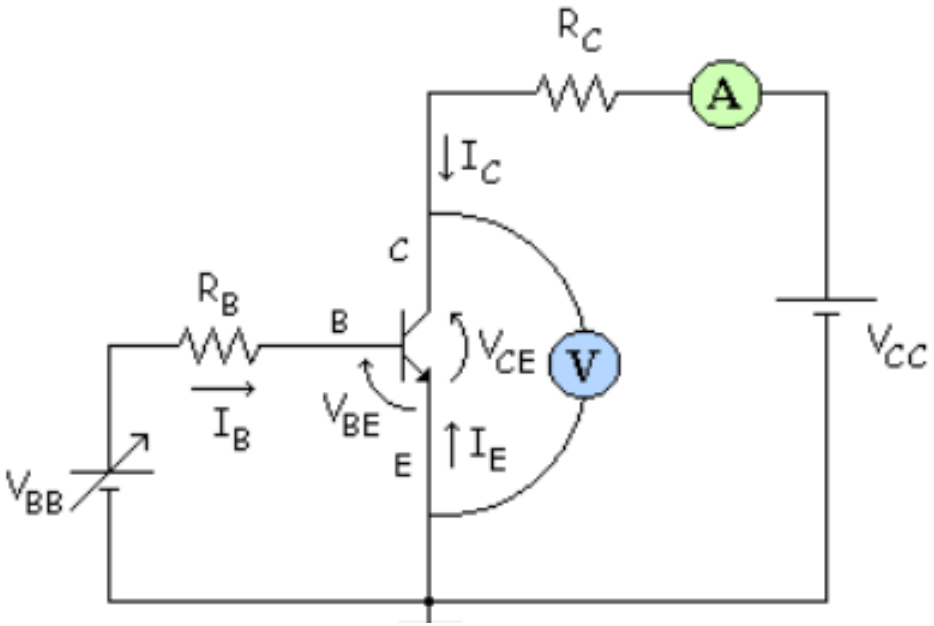
TRANSISTOR

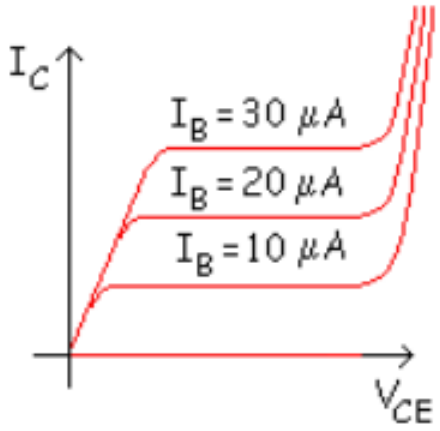
CURVA CARACTERISTICA

DE SALIDA

Características del transistor bipolar

Determinación de la Curva Características de **Salida**

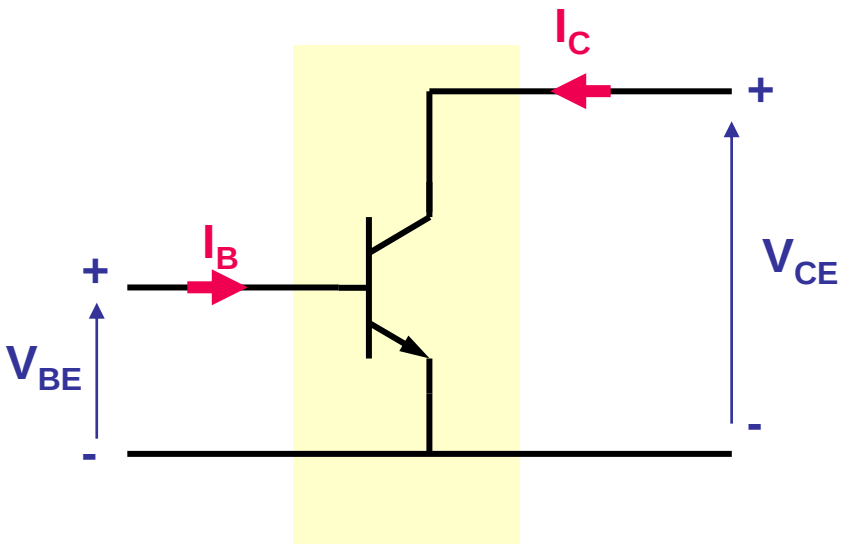


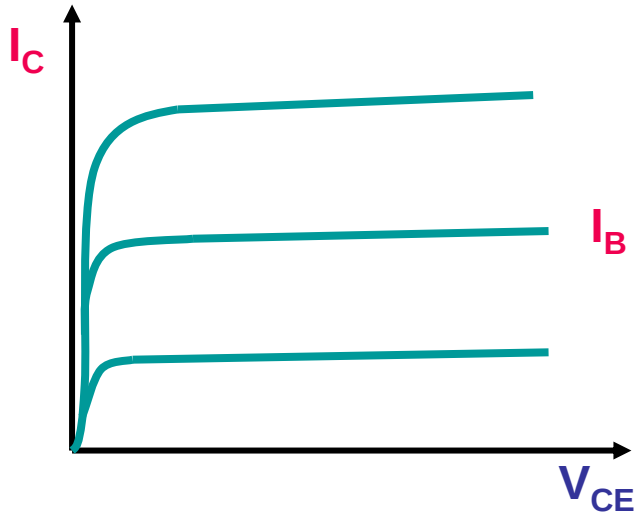


Curvas Características de SALIDA

Transistor NPN

$I_C = f(I_B, V_{CE})$ Característica de salida

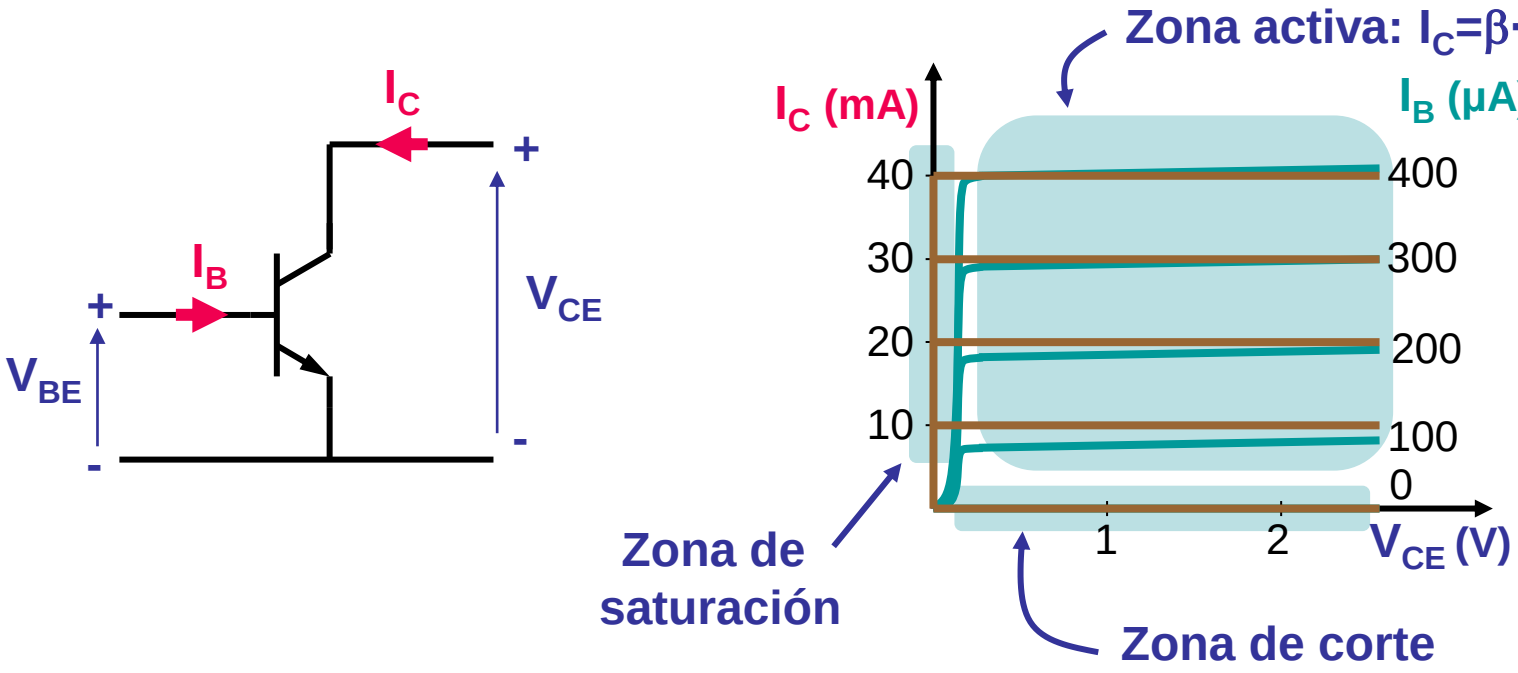




La corriente que circula por el colector se controla mediante la corriente de base I_B.

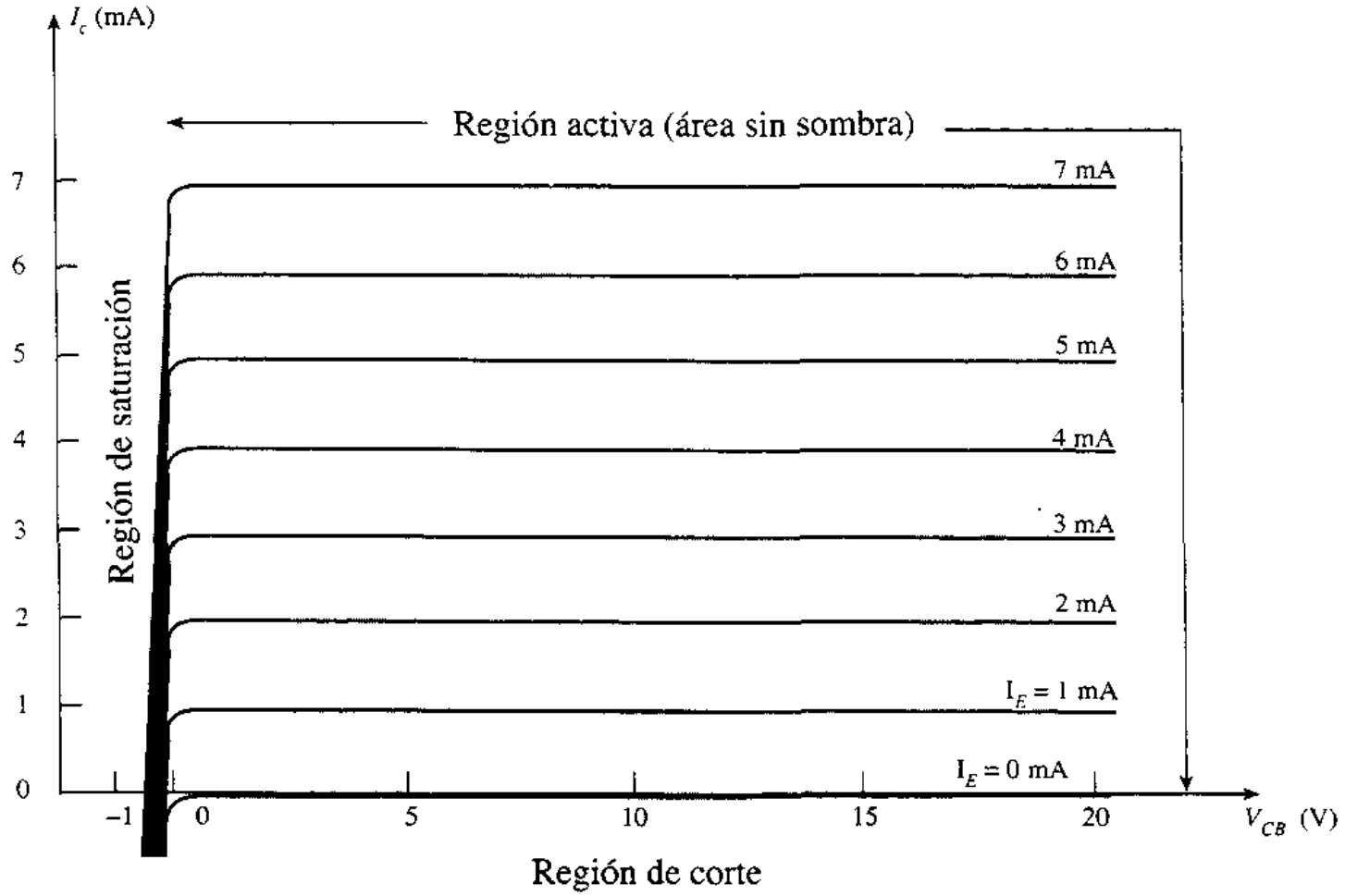
Características eléctricas del transistor bipolar: linealización

Transistor NPN: linealización de la característica de salida



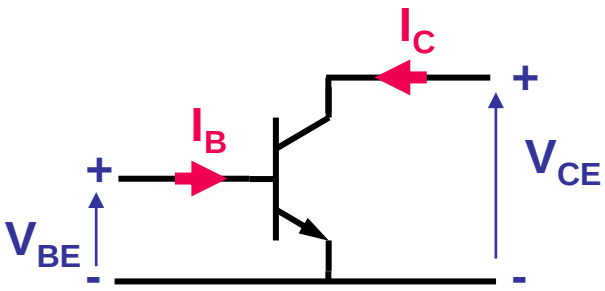
El parámetro fundamental que describe la característica de salida del transistor es la ganancia de corriente β.

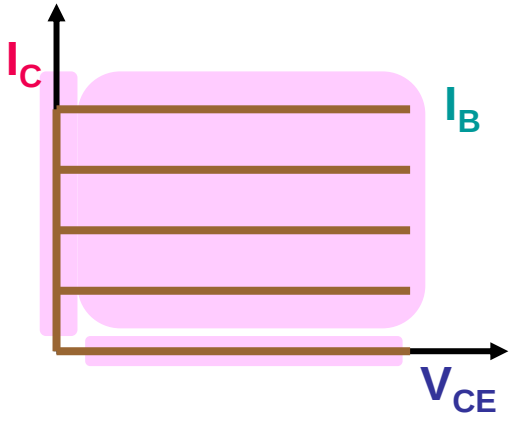
Características de salida

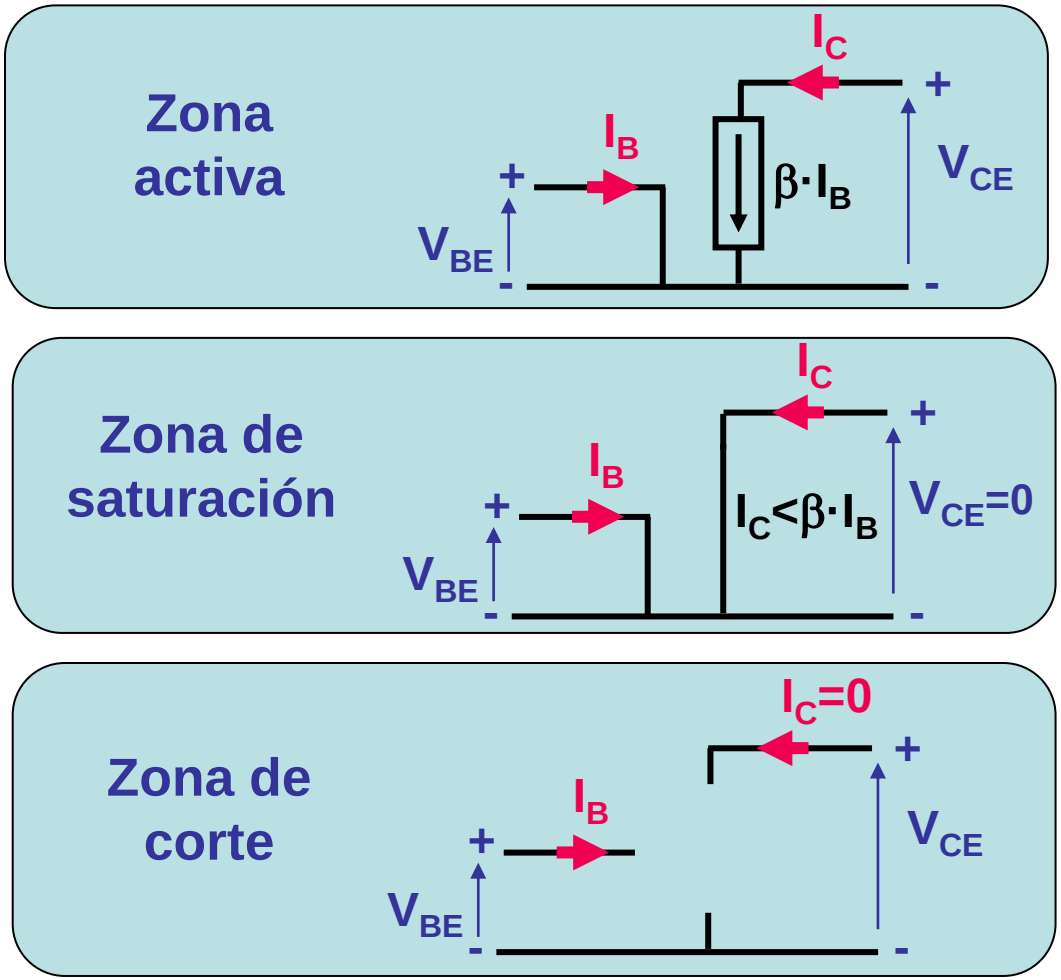


Características del transistor bipolar

Transistor NPN: zonas de funcionamiento del transistor ideal

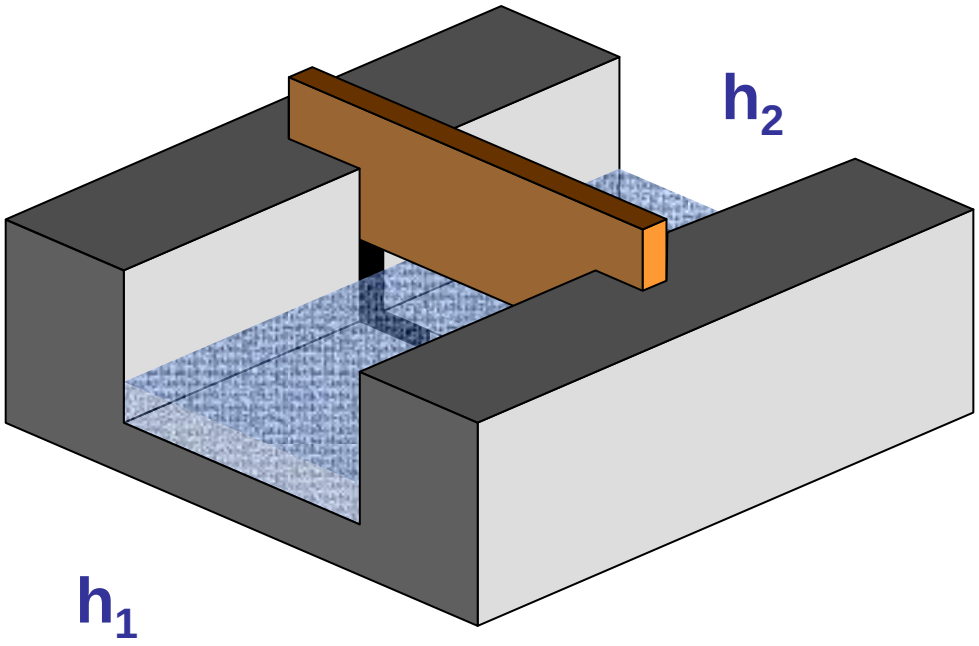


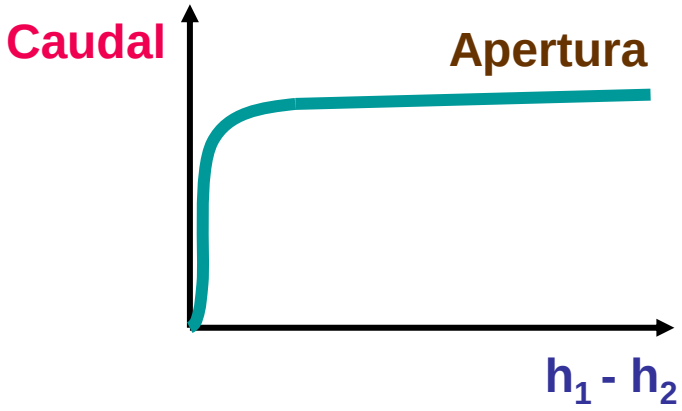




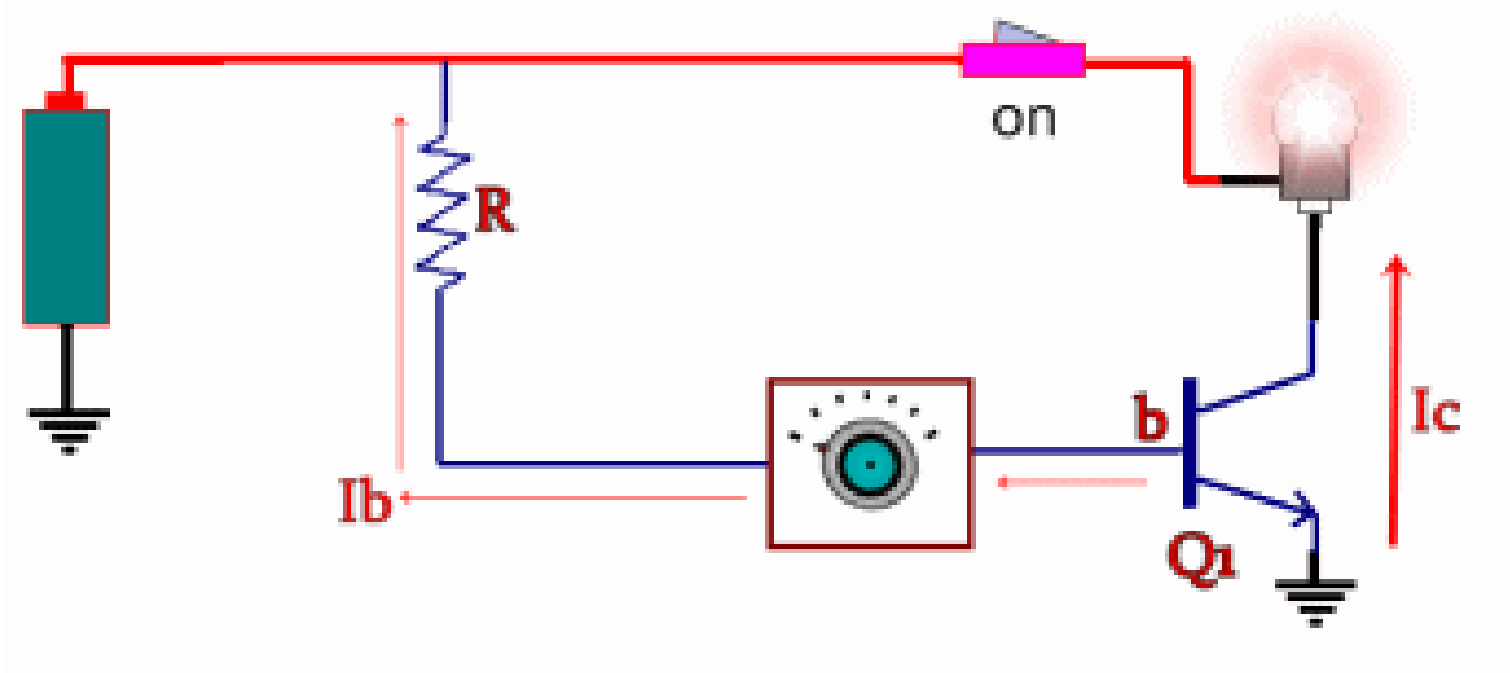
Curvas Características del transistor bipolar

Equivalente hidráulico del transistor en saturación

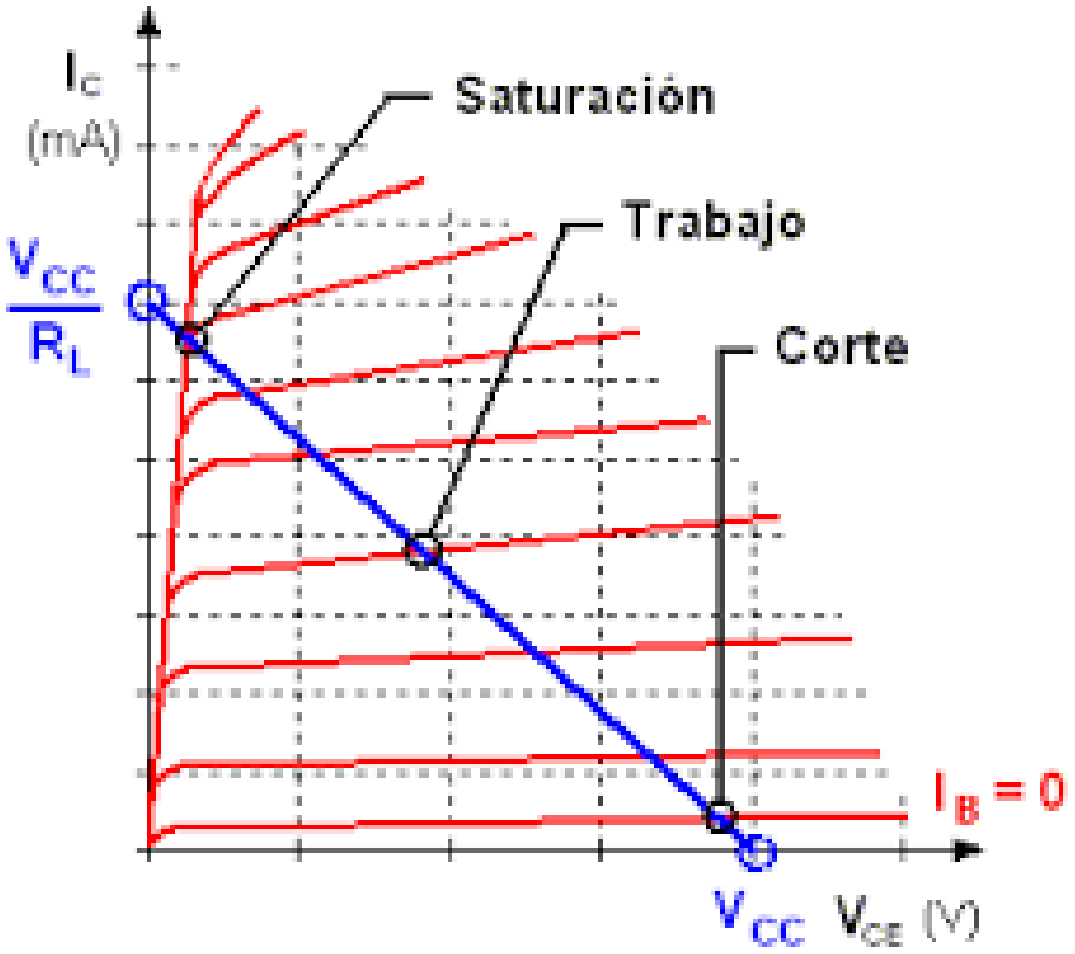




TRANSISTOR: Control Lineal

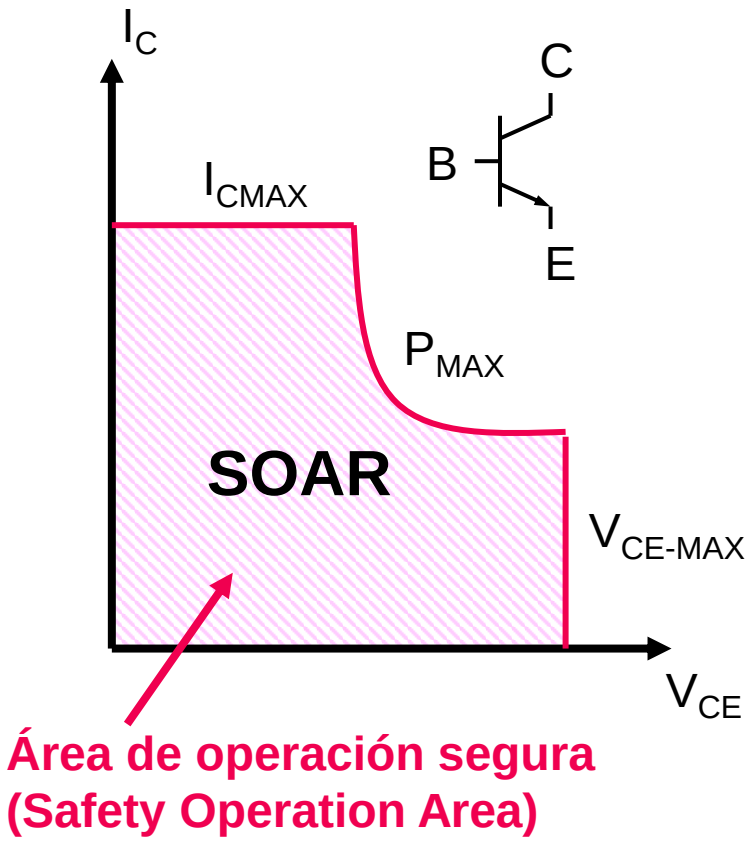


PUNTO "Q" (Punto de Trabajo)

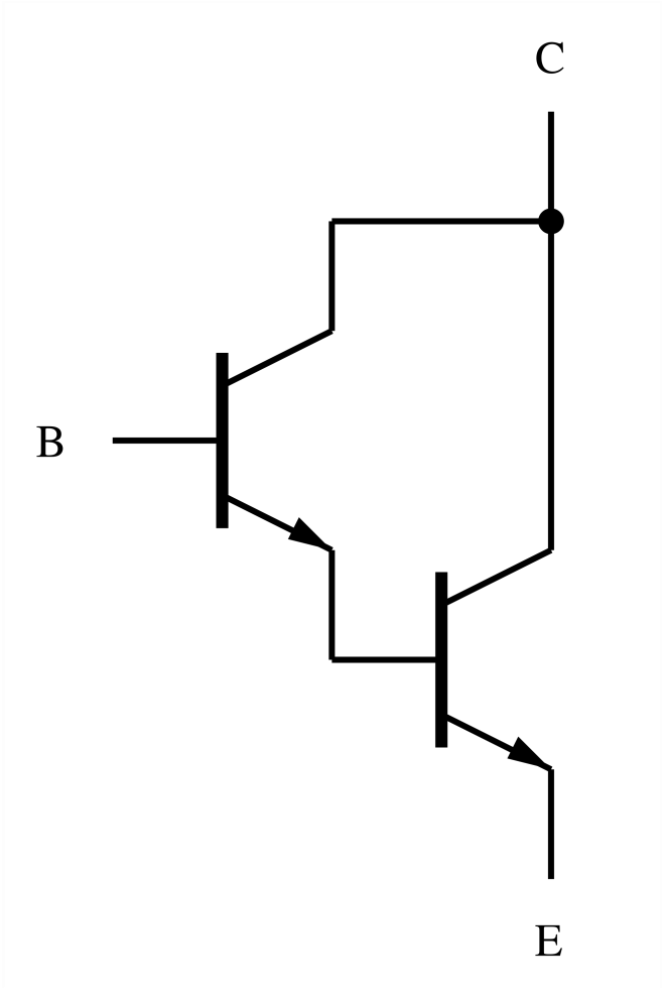


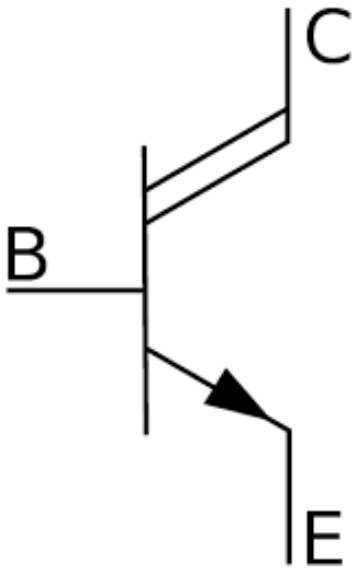
Características reales: datos proporcionados por los fabricantes

$I_{C\text{-}MAX}$	Corriente máxima de colector
$V_{CE\text{-}MAX}$	Tensión máxima CE
P_{MAX}	Potencia máxima
$V_{CE\text{-}SAT}$	Tensión C.E. de saturación
$H_{FE} \cong \beta$	Ganancia

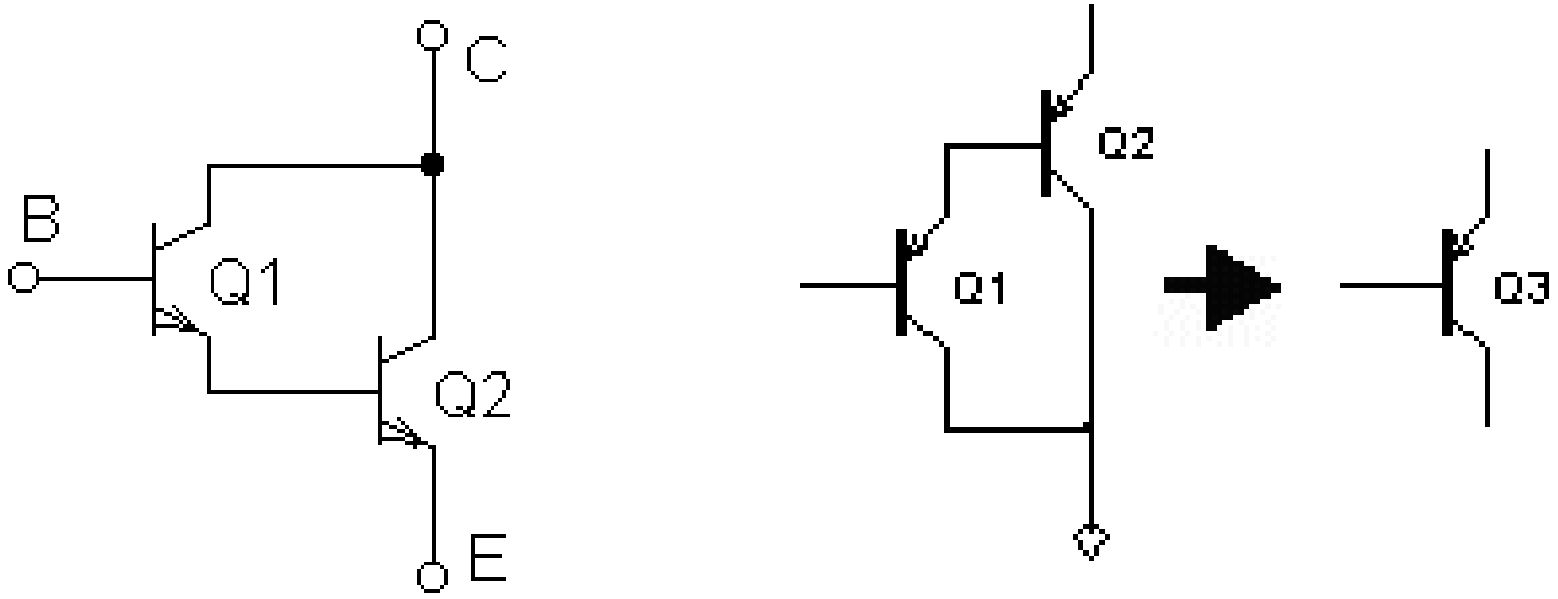


TANSISTOR DARLINGTON

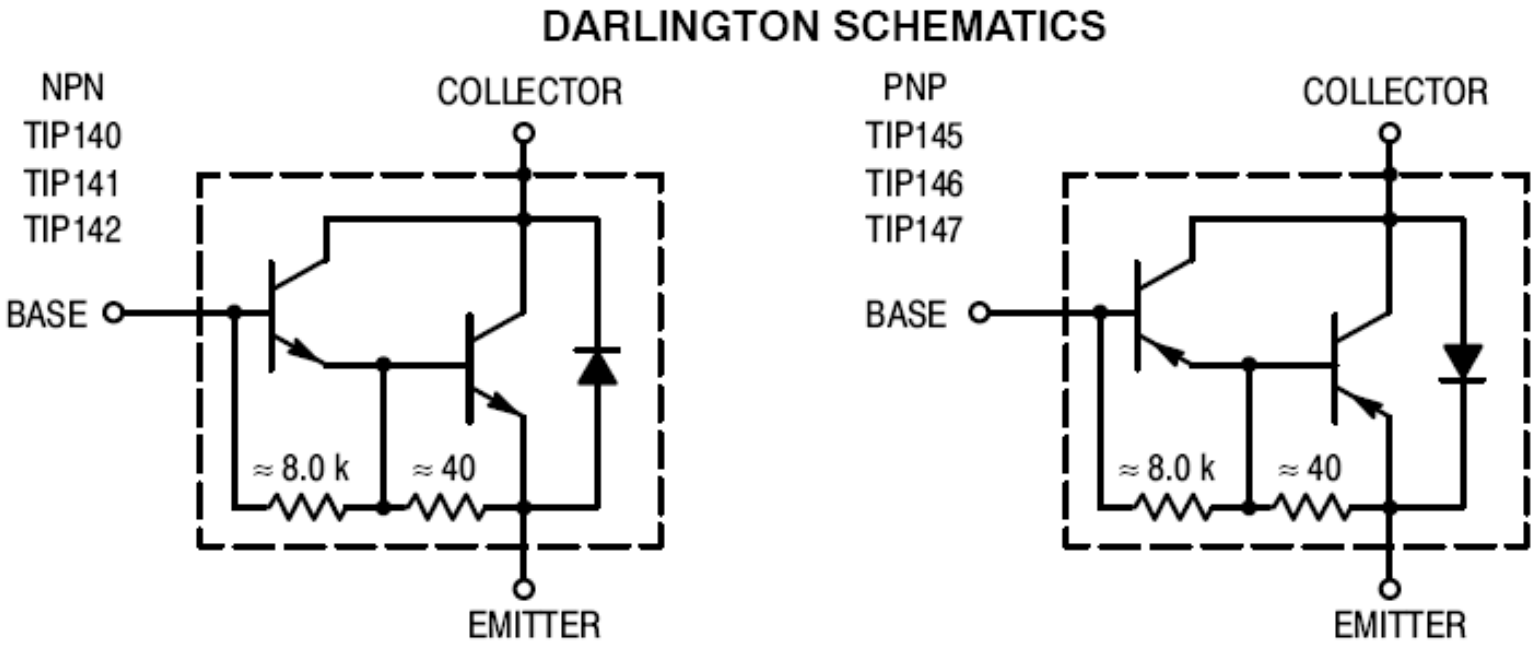




TANSISTOR DARLINGTON



TANSISTOR DARLINGTON



TANSISTOR DARLINGTON

ON CHARACTERISTICS (Note 2)

DC Current Gain (I_C = 5.0 A, V_{CE} = 4.0 V) (I_C = 10 A, V_{CE} = 4.0 V)	h_{FE}	 1000 500	 – –	 – –	–
Collector–Emitter Saturation Voltage (I_C = 5.0 A, I_B = 10 mA) (I_C = 10 A, I_B = 40 mA)	$V_{CE(sat)}$	 – –	 – –	 2.0 3.0	Vdc
Base–Emitter Saturation Voltage (I_C = 10 A, I_B = 40 mA)	$V_{BE(sat)}$	–	–	3.5	Vdc
Base–Emitter On Voltage	$V_{BE(on)}$	–	–	3.0	Vdc

Fin